ADVANTECH

DRAM Memory Module

Portfolio Introduction

PAPS Product Management
Q3 / 2013

PART I.

ADVANTECH QUALIFIED DIMM

(AQD)

ADVANTECH QUALIFIED DIMM

Built to Last ---

The toughest memory module for rigorous applications

QUALITY

RELIABILITY

COMPATIBILITY

LONGEVITY

LIFE-TIME WARRANTY

Quality Assurance Program

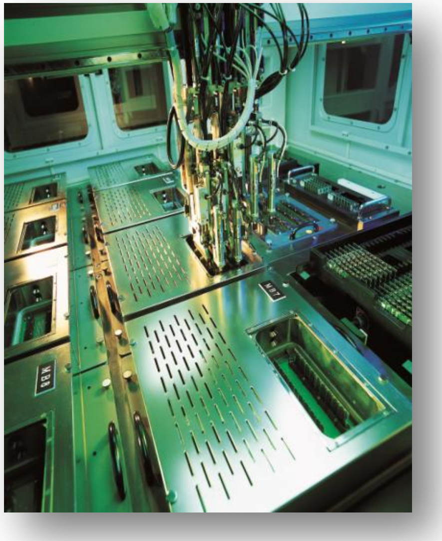
Carefully Selected Premium Materials

ISO-9000 Manufacturing Process

Industrial Testing Standard

Quality Assurance | **Rigorous Reliability Tests** | Cross-Checked Compatibility | Longevity | Life-Time Warranty

- 100% Module On Board Testing
- Vibration Test
- Chamber Test
- Functional Test

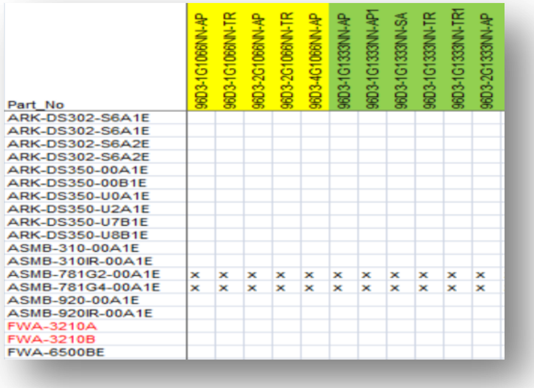


Motherboard Team DOA Testing Result

Memory Compatibility Testing Result

Check & Compare

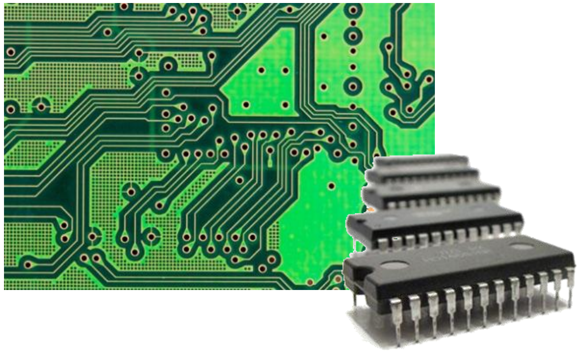
Both Teams Testing Result to Ensure M/B vs. Memory Compatibility



Part_No	96D3-1G1066NN-AP	96D3-1G1066NN-TR	96D3-2G1066NN-AP	96D3-2G1066NN-TR	96D3-4G1066NN-AP	96D3-1G1333NN-AP	96D3-1G1333NN-AP1	96D3-1G1333NN-SA	96D3-1G1333NN-TR	96D3-1G1333NN-TR1	96D3-2G1333NN-AP
ARK-DS302-S6A1E											
ARK-DS302-S6A1E											
ARK-DS302-S6A2E											
ARK-DS302-S6A2E											
ARK-DS350-00A1E											
ARK-DS350-00B1E											
ARK-DS350-U0A1E											
ARK-DS350-U2A1E											
ARK-DS350-U7B1E											
ARK-DS350-U8B1E											
ASMB-310-00A1E											
ASMB-310IR-00A1E											
ASMB-781G2-00A1E	x	x	x	x	x	x	x	x	x	x	x
ASMB-781G4-00A1E	x	x	x	x	x	x	x	x	x	x	x
ASMB-920-00A1E											
ASMB-920IR-00A1E											
FWA-3210A											
FWA-3210B											
FWA-6500BE											

Locked BOM

- IC Spec
- PCB Layout

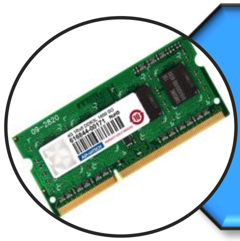


Minimum

3 Years Longevity

Every ADVATECH QUALIFIED DIMM (AQD) is back up by life-time warranty.

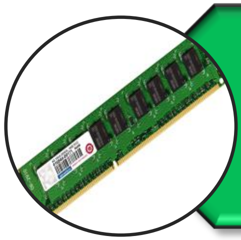
AQD Product Portfolio



Unbuffered DIMM

* General IPC Applications

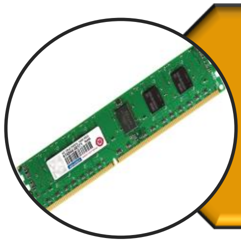
* 1GB, 2GB, 4GB & 8GB



ECC Unbuffered DIMM

* Improve system productivity and efficiency

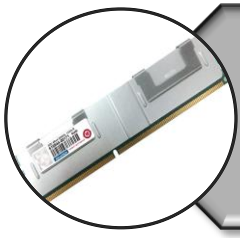
* 4GB & 8GB



Registered DIMM

* Providing the best solution for capacity and performance requirement.

* 8 GB & 16GB



Load Reduce DIMM

* Providing the biggest capacity per server with the lowest energy costs

* 32GB

AQD Products Offering

LONG & SHORT Unbuffered DIMM

LONG DIMM
DDR3-1333
1G

AQD-D31GN13-SX

LONG DIMM
DDR3-1600
2G

AQD-D3L2GN16-SQ

LONG DIMM
DDR3-1600
4G

AQD-D3L4GN16-SQ

LONG DIMM
DDR3-1600
8G

AQD-D3L8GN16-SQ

SHORT DIMM
DDR3-1333
1G

AQD-SD31GN13-SX

SHORT DIMM
DDR3-1600
2G

AQD-SD3L2GN16-SQ

SHORT DIMM
DDR3-1600
4G

AQD-SD3L4GN16-SG

SHORT DIMM
DDR3-1600
8G

AQD-SD3L8GN16-SG

ECC Unbuffered DIMM

LONG DIMM
DDR3-1600
4G

AQD-D3L4GE16-SG

LONG DIMM
DDR3-1600
8G

AQD-D3L8GE16-SG

Registered DIMM

LONG DIMM
DDR3-1600
8G

AQD-D3L8GRV16-SG

LONG DIMM
DDR3-1600
16GB

AQD-D3L16RV16-SM

Load Reduce DIMM

DDR3-1333
32G

AQD-D3L32L13-SM

Part Number Decoder

A Q D – S D 3 L 2 G N V 1 6 – S G

PRODUCT NAME	TYPE	VOLTAGE	CAPACITY	ADVNCED FEATURE	Height	SPEED	FAB	VERSION
A Q D	S D 3	L	2 G	N	V	1 6	S	G
A=Advantech Q=Qualified D=DIMM	DM=SDRAM DIMM DR=DDR D2=DDR2 D3=DDR3 SS=SDRAM SO-DIMM SD=DDR SO-DIMM SD2=DDR2 SO-DIMM SD3=DDR3 SO-DIMM	Blank= 1.5V L=1.35V U=1.25V	1G=1GB 2G=2GB 4G=4GB 8G=8GB 16 =16GB 32 =32GB 64= 64GB	N= NON-ECC and NON REGISTER R= REGISTER E= ECC ONLY L=Load reduce	V= VLP	40=400Mt/s 53=533Mt/s 66=667Mt/s 80=800Mt/s 10=1066Mt/s 13=1333Mt/s 16=1600Mt/s 18=1866Mt/s	S=Samsung H=Hynix M=Micron /Elpida N=Nanya	X=1Gb(128Mx8) T=1Gb(256Mx4) Q=2Gb(256Mx8) Y=2Gb(512Mx4) G=4Gb(512Mx8) Z= 4Gb(1Gbx4) M=8Gb(2Gbx4)

Color / Symbol Key

■ **Available** ▨ **Phasing-out** □ **Planning**

E **ECC** R **Registered** F **Fully Buffered** N **New**

LR **Load-Reduce** V **Very Low-Profile** W **Wide Temperature** LV **Low-Voltage**

AQD DDR3 Memory Modules Portfolio

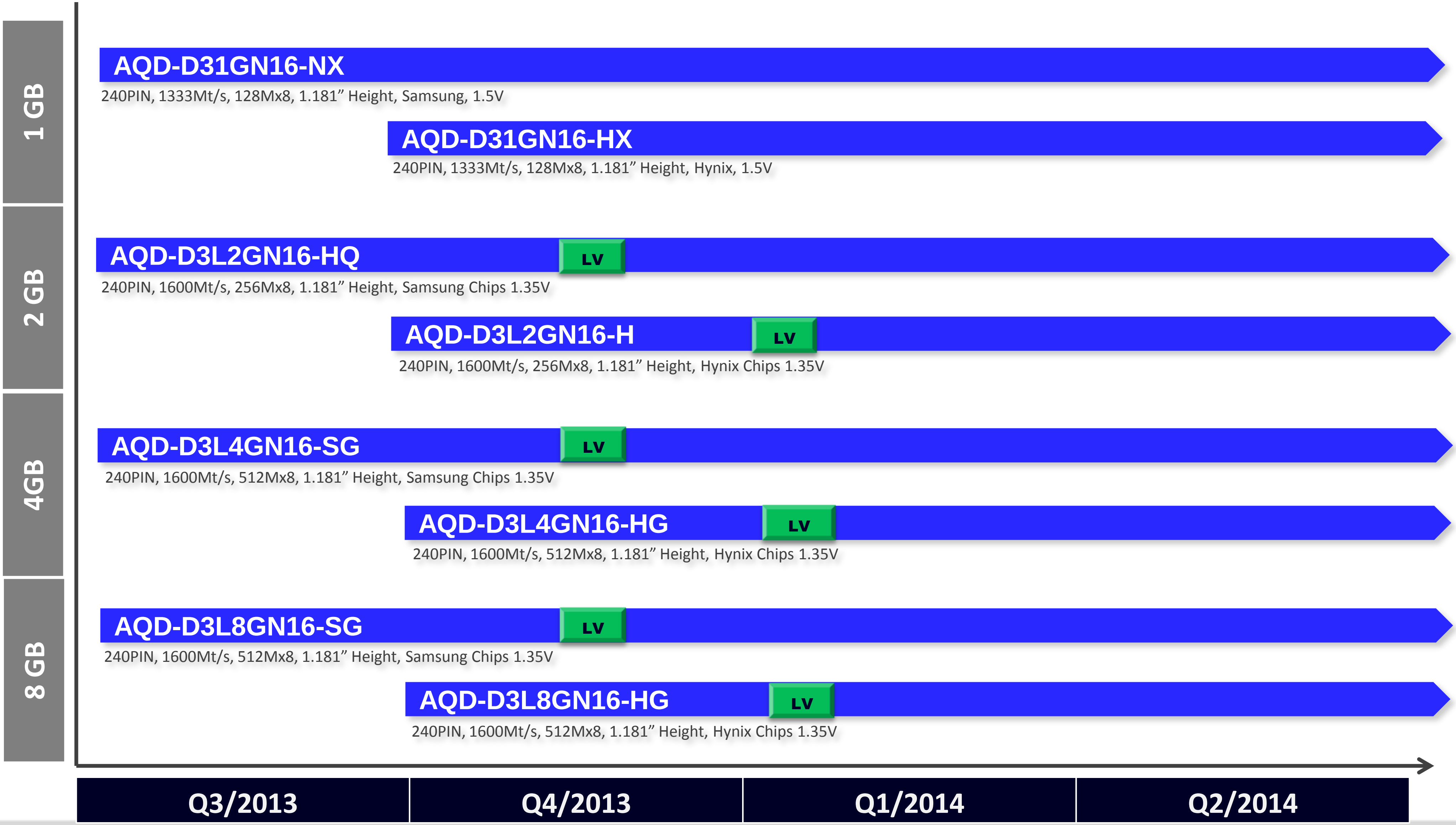
DDR3 **1.35 Low Voltage**		1333		1600	
		LONG	SHORT	LONG	SHORT
U-DIMM	1GB (128X8)	AQD-D31GN13-SX (1.5V)	AQD-SD31GN13-SX (1.5V)		
	2GB (256MX8)			AQD-D3L2GN16-SQ	AQD-SD3L2GN16-SQ
	4GB (512MX8)			AQD-D3L4GN16-SG	AQD-SD3L4GN16-SG
	8GB (512MX8)			AQD-D3L8GN16-SG	AQD-SD3L8GN16-SG
ECC U-DIMM	4GB (512MX8)			AQD-D3L4GE16-SG	
	8GB (512MX8)			AQD-D3L8GE16-SG	
R-DIMM	4GB (512MX8)				
	8GB (512MX8)			AQD-D3L8GRV16-SG	
	16GB(2Gbx4)			AQD-D3L16RV16-SM	
LOAD REDUCE	32GB (2GbX4)	AQD-D3L32L13-SM			

■ Available ■ Phasing-out □ Planning

E ECC R Registered F Fully Buffered N New

LR Load-Reduce V Very Low-Profile W Wide Temperature LV Low-Voltage

DDR3 DIMM



1 GB

AQD-D31GN16-NX
240PIN, 1333Mt/s, 128Mx8, 1.181" Height, Samsung, 1.5V

AQD-D31GN16-HX
240PIN, 1333Mt/s, 128Mx8, 1.181" Height, Hynix, 1.5V

2 GB

AQD-D3L2GN16-HQ LV
240PIN, 1600Mt/s, 256Mx8, 1.181" Height, Samsung Chips 1.35V

AQD-D3L2GN16-H LV
240PIN, 1600Mt/s, 256Mx8, 1.181" Height, Hynix Chips 1.35V

4GB

AQD-D3L4GN16-SG LV
240PIN, 1600Mt/s, 512Mx8, 1.181" Height, Samsung Chips 1.35V

AQD-D3L4GN16-HG LV
240PIN, 1600Mt/s, 512Mx8, 1.181" Height, Hynix Chips 1.35V

8 GB

AQD-D3L8GN16-SG LV
240PIN, 1600Mt/s, 512Mx8, 1.181" Height, Samsung Chips 1.35V

AQD-D3L8GN16-HG LV
240PIN, 1600Mt/s, 512Mx8, 1.181" Height, Hynix Chips 1.35V

Q3/2013	Q4/2013	Q1/2014	Q2/2014

DDR3 SO-DIMM

🟨 Available ▨ Phasing-out 🟧 Planning

E ECC
R Registered
F Fully Buffered
N New
LR Load-Reduce
V Very Low-Profile
W Wide Temperature
LV Low-Voltage

1 GB

AQD-SD31GN16-SX
204PIN, 1333Mt/s, 128Mx8, 1.181" Height, Samsung Chips 1.5V

AQD-SD31GN16-HX
204PIN, 1333Mt/s, 128Mx8, 1.181" Height, Hynix Chips 1.5V

2 GB

AQD-SD3L2GN16-SQ LV
204PIN, 1600Mt/s, 256Mx8, 1.181" Height, Samsung Chips 1.35V

AQD-SD3L2GN16-HQ LV
204PIN, 1600Mt/s, 256Mx8, 1.181" Height, Hynix, Chips 1.35V

4GB

AQD-SD3L4GN16-SG LV
204PIN, 1600Mt/s, 512Mx8, 1.181" Height, Samsung Chips 1.35V

AQD-SD3L4GN16-HG LV
204PIN, 1600s, 512Mx8, 1.181" Height, Hynix Chips 1.35V

8 GB

AQD-SD3L8GN16-SG LV
204PIN, 1600Mt/s, 512Mx8, 1.181" Height, Samsung, Chips 1.35V

AQD-SD3L8GN16-HG LV
204PIN, 1600Mt/s, 512Mx8, 1.181" Height, Hynix, Chips 1.35V

Q3/2013 | Q4/2013 | Q1/2014 | Q2/2014

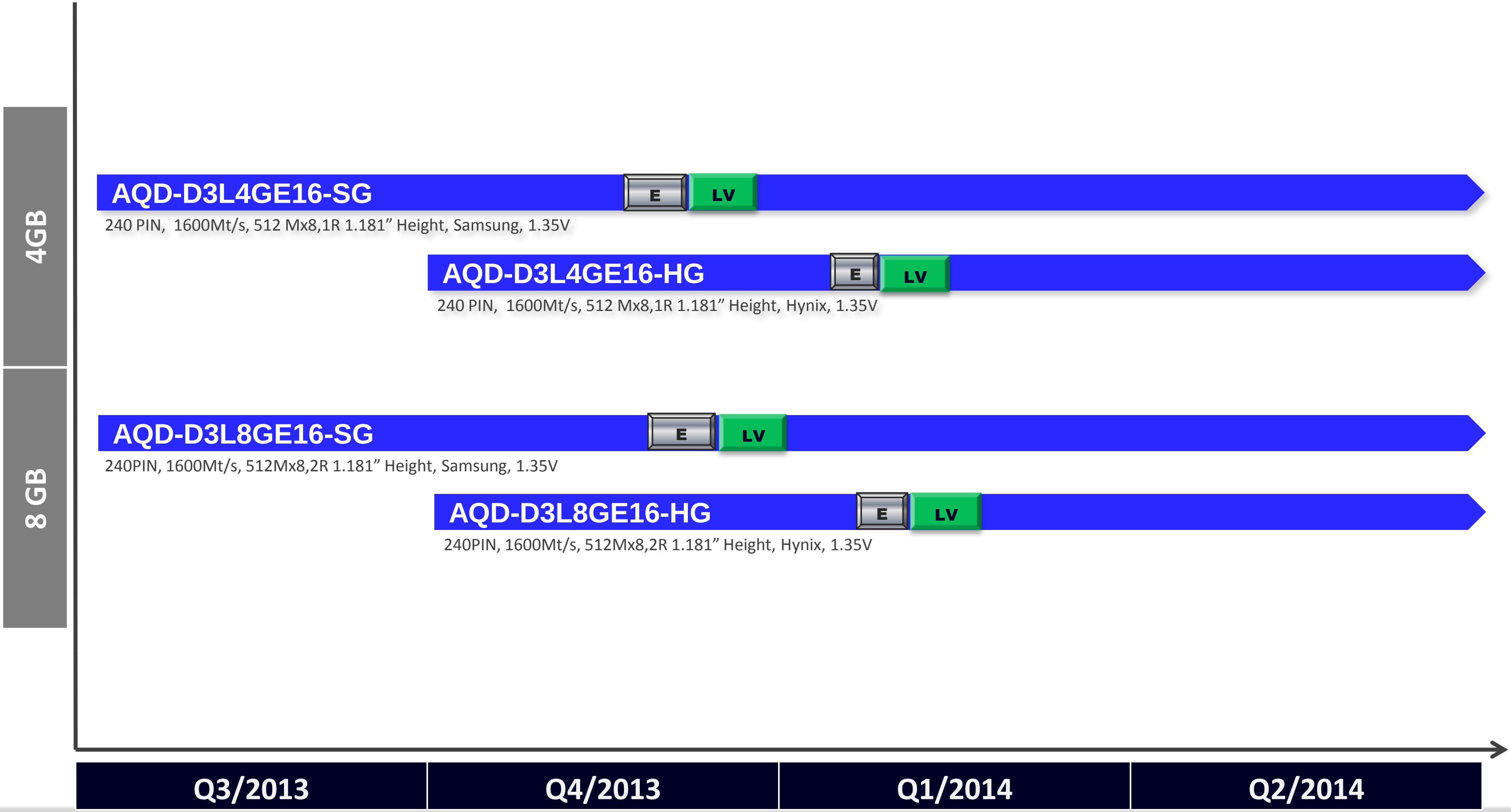
DDR3 DIMM Advance Feature

ECC

Available · Phasing-out · Planning

E ECC · R Registered · F Fully Buffered · N New

LR Load-Reduce · V Very Low-Profile · W Wide Temperature · LV Low-Voltage



AQD-D3L4GE16-SG
240 PIN, 1600Mt/s, 512 Mx8,1R 1.181” Height, Samsung, 1.35V

AQD-D3L4GE16-HG
240 PIN, 1600Mt/s, 512 Mx8,1R 1.181” Height, Hynix, 1.35V

AQD-D3L8GE16-SG
240PIN, 1600Mt/s, 512Mx8,2R 1.181” Height, Samsung, 1.35V

AQD-D3L8GE16-HG
240PIN, 1600Mt/s, 512Mx8,2R 1.181” Height, Hynix, 1.35V

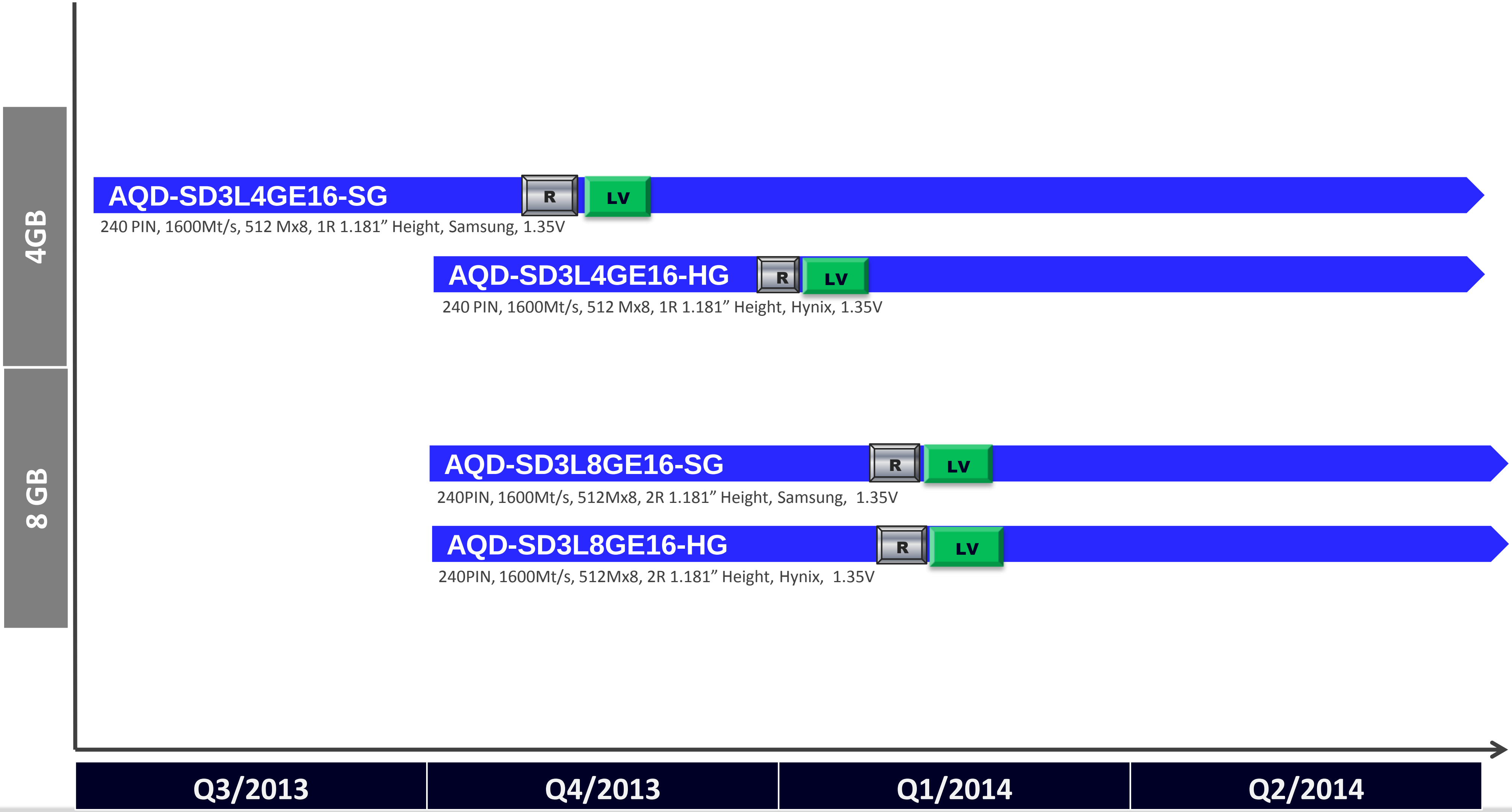
DDR3 SO DIMM Advance Feature

Available · Phasing-out · Planning

E ECC · R Registered · F Fully Buffered · N New

LR Load-Reduce · V Very Low-Profile · W Wide Temperature · LV Low-Voltage

ECC

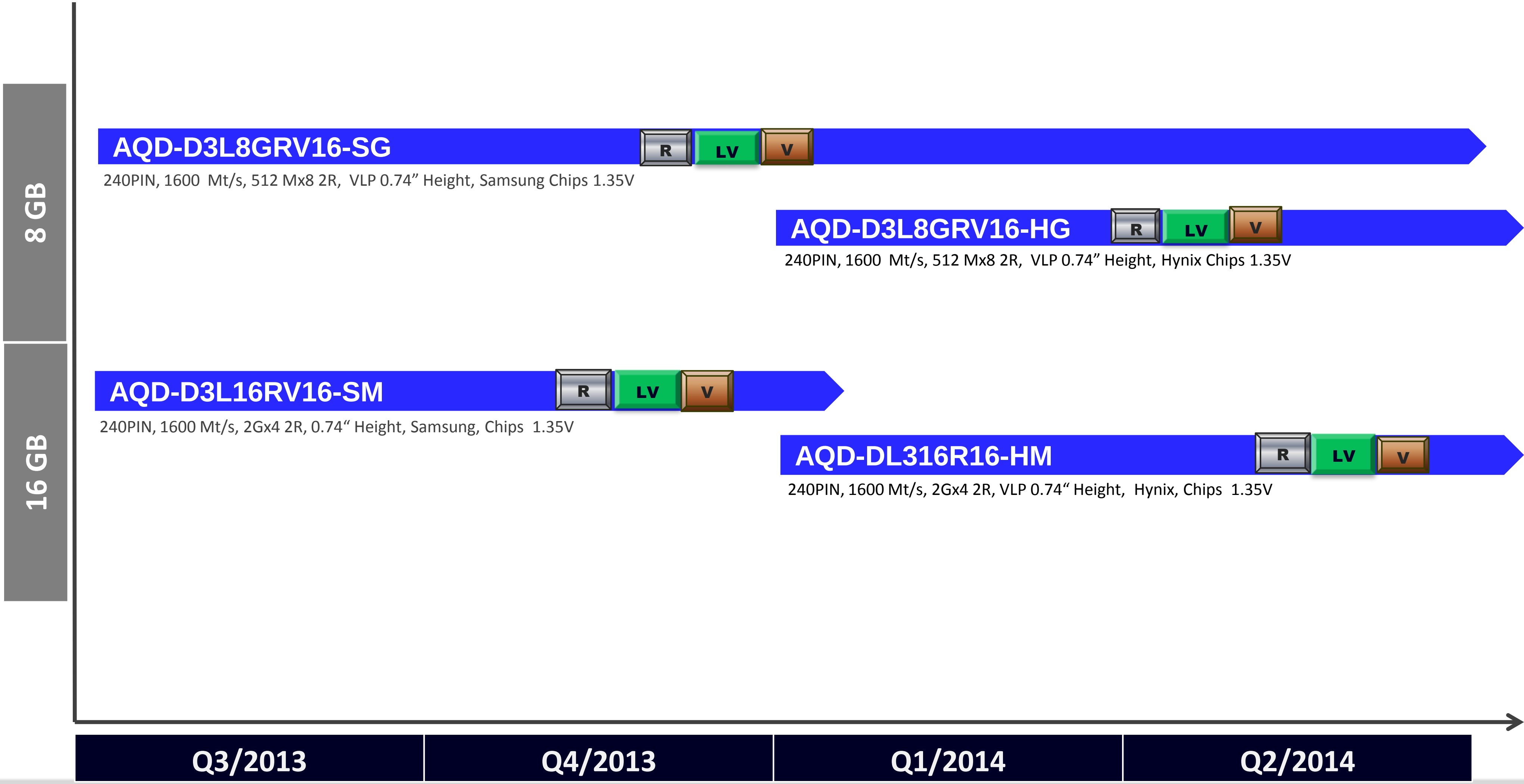


🟨 Available ▨ Phasing-out 🟧 Planning

E ECC
R Registered
F Fully Buffered
N New
LR Load-Reduce
V Very Low-Profile
W Wide Temperature
LV Low-Voltage

DDR3 DIMM Advance Feature

ECC and Registered



8 GB

AQD-D3L8GRV16-SG R LV V

240PIN, 1600 Mt/s, 512 Mx8 2R, VLP 0.74" Height, Samsung Chips 1.35V

AQD-D3L8GRV16-HG R LV V

240PIN, 1600 Mt/s, 512 Mx8 2R, VLP 0.74" Height, Hynix Chips 1.35V

16 GB

AQD-D3L16RV16-SM R LV V

240PIN, 1600 Mt/s, 2Gx4 2R, 0.74" Height, Samsung, Chips 1.35V

AQD-DL316R16-HM R LV V

240PIN, 1600 Mt/s, 2Gx4 2R, VLP 0.74" Height, Hynix, Chips 1.35V

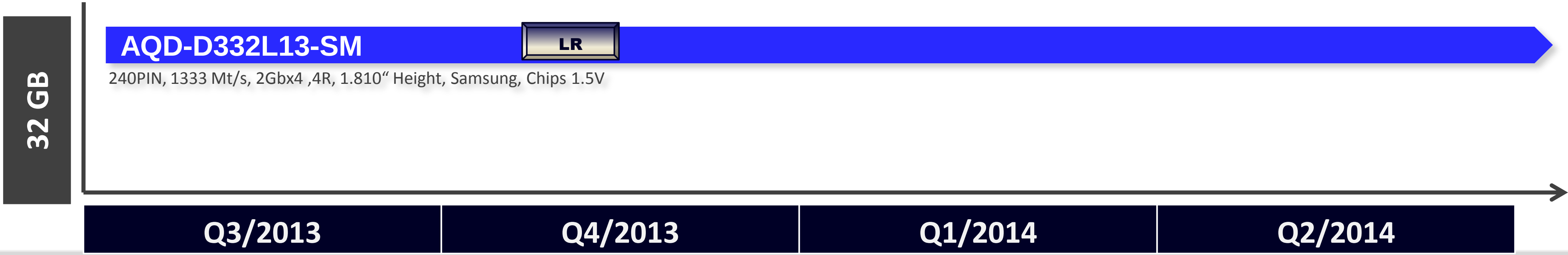
Q3/2013 | Q4/2013 | Q1/2014 | Q2/2014

🟨 Available ▨ Phasing-out 🟨 Planning

E ECC
R Registered
F Fully Buffered
N New
LR Load-Reduce
V Very Low-Profile
W Wide Temperature
LV Low-Voltage

DDR3 DIMM Advance Feature

Load Reduce



AQD-D332L13-SM

240PIN, 1333 Mt/s, 2Gbx4 ,4R, 1.810“ Height, Samsung, Chips 1.5V

PART II,

96 PARTS MEMORY MODULE

Part Number Decoder

9 6 D M – 6 4 M 1 0 0 N N – A P

Memory Type

DM=SDRAM DIMM
DR=DDR
DRI=INDUSTRIAL GRADE DDR
D2=DDR2
D2I=INDUSTRIAL GRADE DDR2
D3=DDR3
SS=SDRAM SO-DIMM
SD=DDR SO-DIMM
SDI=INDUSTRIAL GRADE SO-DDR
SD2=DDR2 SO-DIMM
SD2I=INDUSRIAL GRADE SO-DDR2
SD3=DDR3 SO-DIMM
SD3I=INDUSTRIAL GRADE SO-DDR3

Capacity

64M=64MB
128M=128MB
256M=256MB
512M=512MB
1G=1GB
2G=2GB
4G=4GB
8G=8GB

Speed

100=100Mb/s
133=133Mb/s
266=266Mb/s
333=333Mb/s
400=400Mb/s
533=533Mb/s
667=667Mb/s
800=800Mb/s
1066=1066Mb/s
1333=1333Mbs

Advance Feature

NN=
NON-ECC and NON-REGISTER
ER=
ECC AND REGISTER
E=
ECC ONLY

Manufacturer

AP=APACER
ATL=ATP
DA=DATA
IK=INNODISK
KI=KINGSTON
MI=MIRCON
SB=SWISSBIT
TR=TRANSCEND
VI=VIRTIUM

Color / Symbol Key

■ Available ■ Phasing-out □ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature

SDRAM DIMM

▨ Available ▨ Phasing-out ▨ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature

64 MB

96DM-64M133NN-TR1 L

Transcend, 168PIN, 133Mb/s, 8Mx16, 0.905” Height, Samsung Chips

128 MB

96DM-128M133NN-TR

Transcend, 168PIN, 133Mb/s, 8Mx16, 1.250” Height, Samsung Chips

256 MB

96DM-256M133NN-TR

Transcend, 168PIN, 133Mb/s, 32Mx8, 1.150” Height, Samsung Chips

512 MB

96DM-512M133NN-TR

Transcend, 168PIN, 133Mb/s, 32Mx8, 1.150” Height, Samsung Chips

Q3/2013	Q4/2013	Q1/2014	Q2/2014

SDRAM SO-DIMM

🟦 Available ▨ Phasing-out ▭ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature

96SS-64M133NN-TR L

Transcend, 144PIN, 133Mb/s, 8Mx16, 0.945” Height, Samsung Chips

96SS-128M133NN-TR

Transcend, 144PIN, 133Mb/s, 8Mx16, 1.150” Height, Samsung Chips

96SS-128M133NN-TR1 L

Transcend, 144PIN, 133Mb/s, 16Mx16, 0.945” Height, Samsung Chips

96SS-256M133NN-TR

Transcend, 144PIN, 133Mb/s, 16Mx16, 1.250” Height, Samsung Chips

96SS-256M133NN-TR3

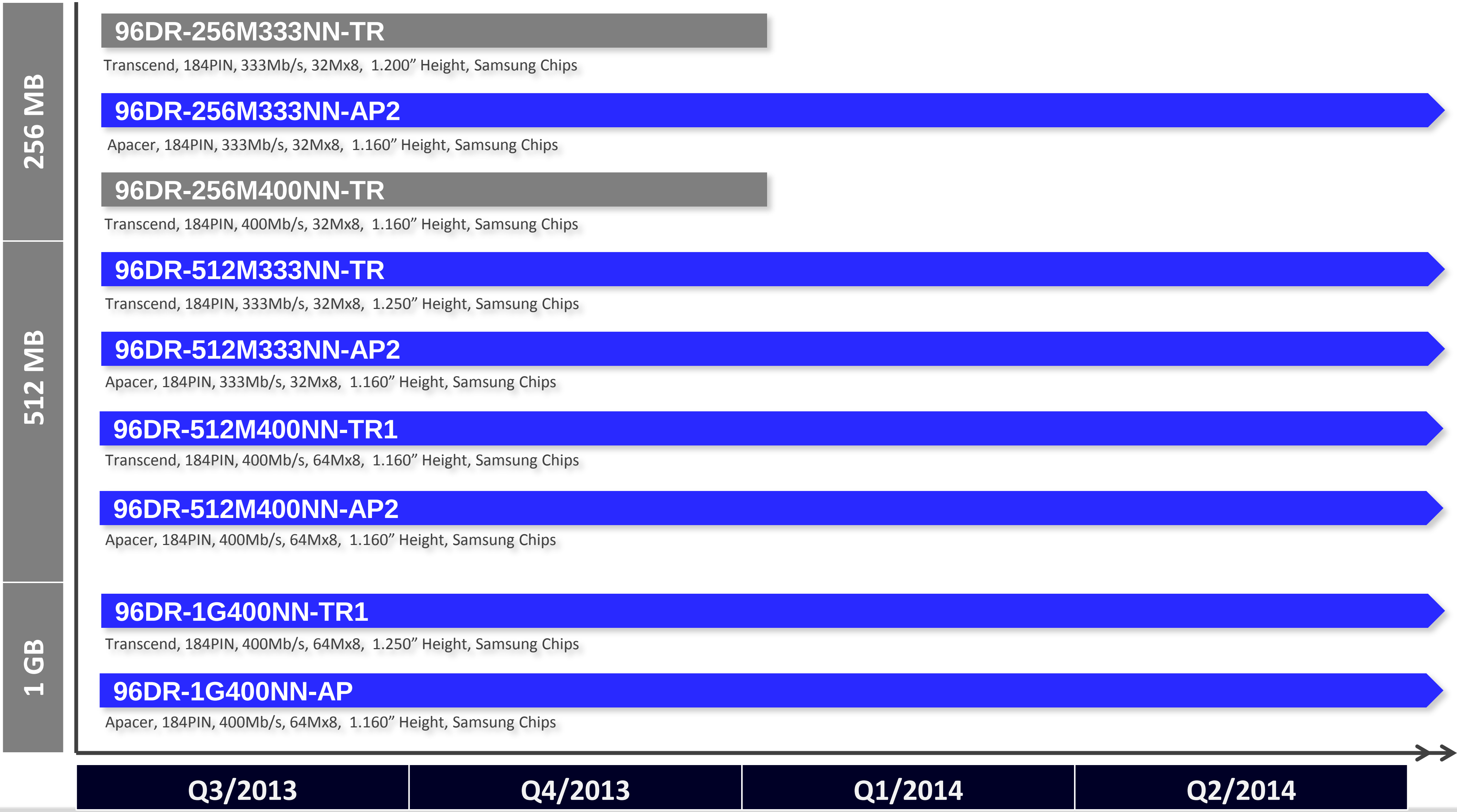
Transcend, 144PIN, 133Mb/s, 32Mx8, 1.150” Height, Samsung Chips

DDR DIMM

▬ Available ▬ Phasing-out ▬ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature



96DR-256M333NN-TR

Transcend, 184PIN, 333Mb/s, 32Mx8, 1.200” Height, Samsung Chips

96DR-256M333NN-AP2

Apacer, 184PIN, 333Mb/s, 32Mx8, 1.160” Height, Samsung Chips

96DR-256M400NN-TR

Transcend, 184PIN, 400Mb/s, 32Mx8, 1.160” Height, Samsung Chips

96DR-512M333NN-TR

Transcend, 184PIN, 333Mb/s, 32Mx8, 1.250” Height, Samsung Chips

96DR-512M333NN-AP2

Apacer, 184PIN, 333Mb/s, 32Mx8, 1.160” Height, Samsung Chips

96DR-512M400NN-TR1

Transcend, 184PIN, 400Mb/s, 64Mx8, 1.160” Height, Samsung Chips

96DR-512M400NN-AP2

Apacer, 184PIN, 400Mb/s, 64Mx8, 1.160” Height, Samsung Chips

96DR-1G400NN-TR1

Transcend, 184PIN, 400Mb/s, 64Mx8, 1.250” Height, Samsung Chips

96DR-1G400NN-AP

Apacer, 184PIN, 400Mb/s, 64Mx8, 1.160” Height, Samsung Chips

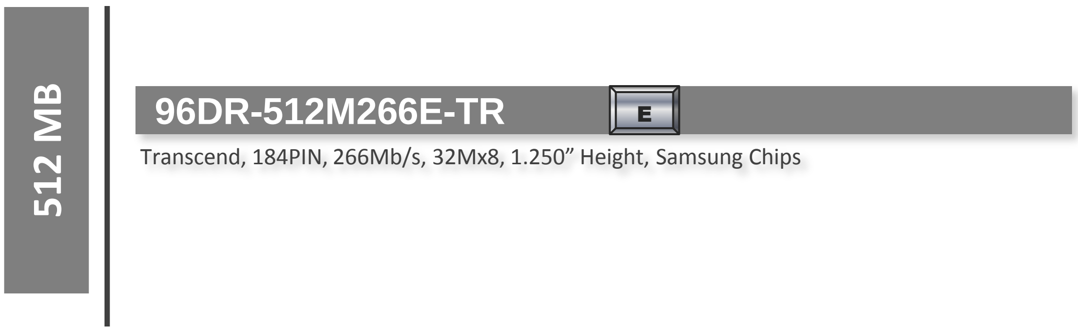
DDR DIMM Advance Feature

🟦 Available ▨ Phasing-out ⬜ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature

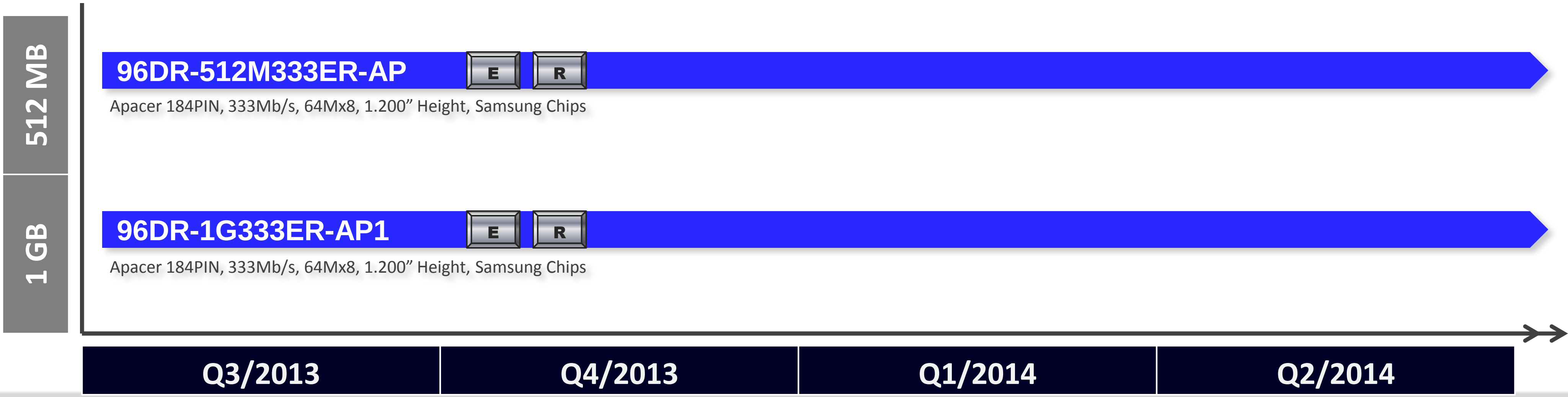
ECC



96DR-512M266E-TR

Transcend, 184PIN, 266Mb/s, 32Mx8, 1.250” Height, Samsung Chips

ECC and Registered



96DR-512M333ER-AP

Apacer 184PIN, 333Mb/s, 64Mx8, 1.200” Height, Samsung Chips

96DR-1G333ER-AP1

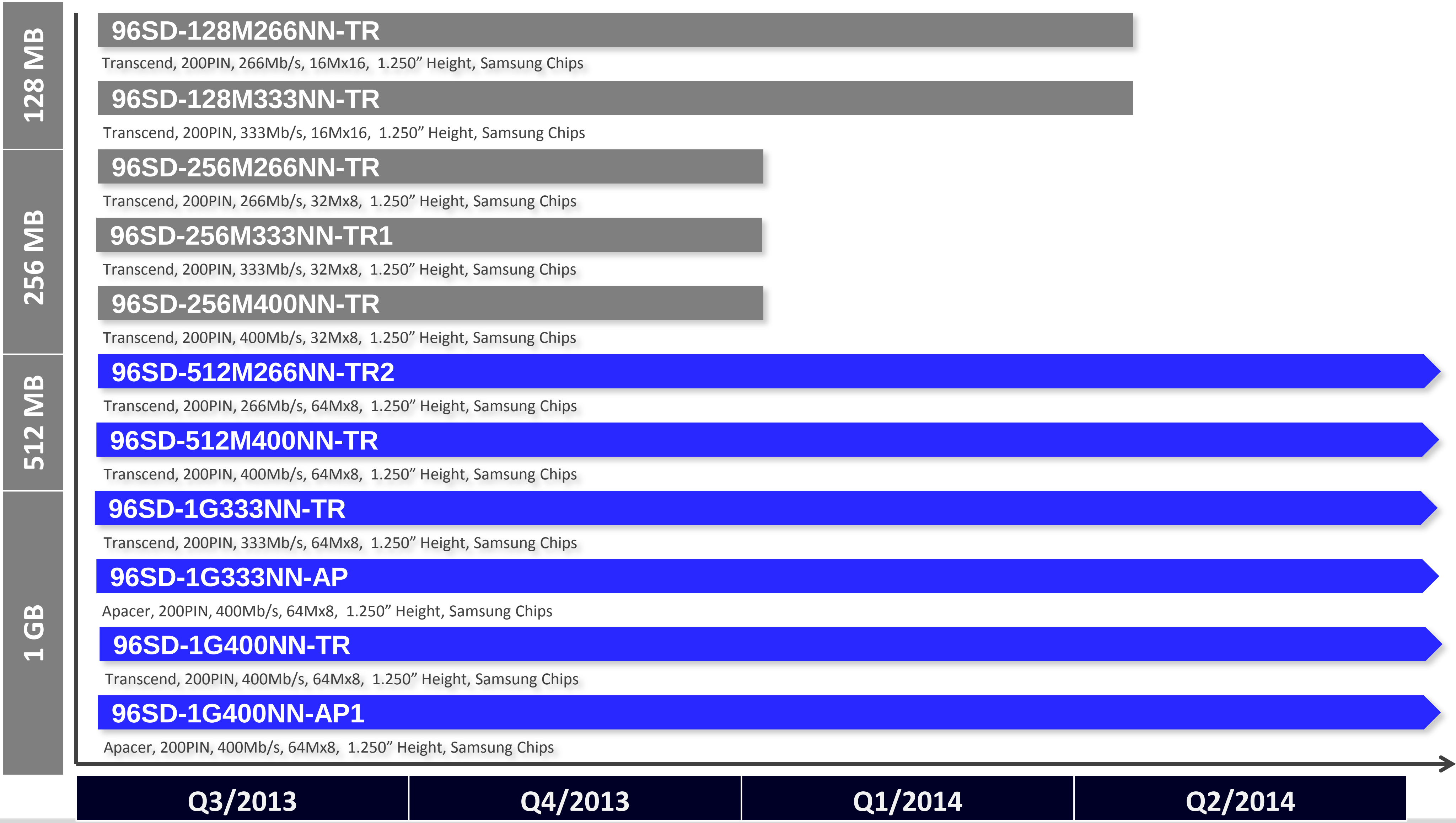
Apacer 184PIN, 333Mb/s, 64Mx8, 1.200” Height, Samsung Chips

DDR SO-DIMM

🟦 Available ▨ Phasing-out ▭ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature



128 MB

96SD-128M266NN-TR
Transcend, 200PIN, 266Mb/s, 16Mx16, 1.250” Height, Samsung Chips

96SD-128M333NN-TR
Transcend, 200PIN, 333Mb/s, 16Mx16, 1.250” Height, Samsung Chips

256 MB

96SD-256M266NN-TR
Transcend, 200PIN, 266Mb/s, 32Mx8, 1.250” Height, Samsung Chips

96SD-256M333NN-TR1
Transcend, 200PIN, 333Mb/s, 32Mx8, 1.250” Height, Samsung Chips

96SD-256M400NN-TR
Transcend, 200PIN, 400Mb/s, 32Mx8, 1.250” Height, Samsung Chips

512 MB

96SD-512M266NN-TR2
Transcend, 200PIN, 266Mb/s, 64Mx8, 1.250” Height, Samsung Chips

96SD-512M400NN-TR
Transcend, 200PIN, 400Mb/s, 64Mx8, 1.250” Height, Samsung Chips

1 GB

96SD-1G333NN-TR
Transcend, 200PIN, 333Mb/s, 64Mx8, 1.250” Height, Samsung Chips

96SD-1G333NN-AP
Apacer, 200PIN, 400Mb/s, 64Mx8, 1.250” Height, Samsung Chips

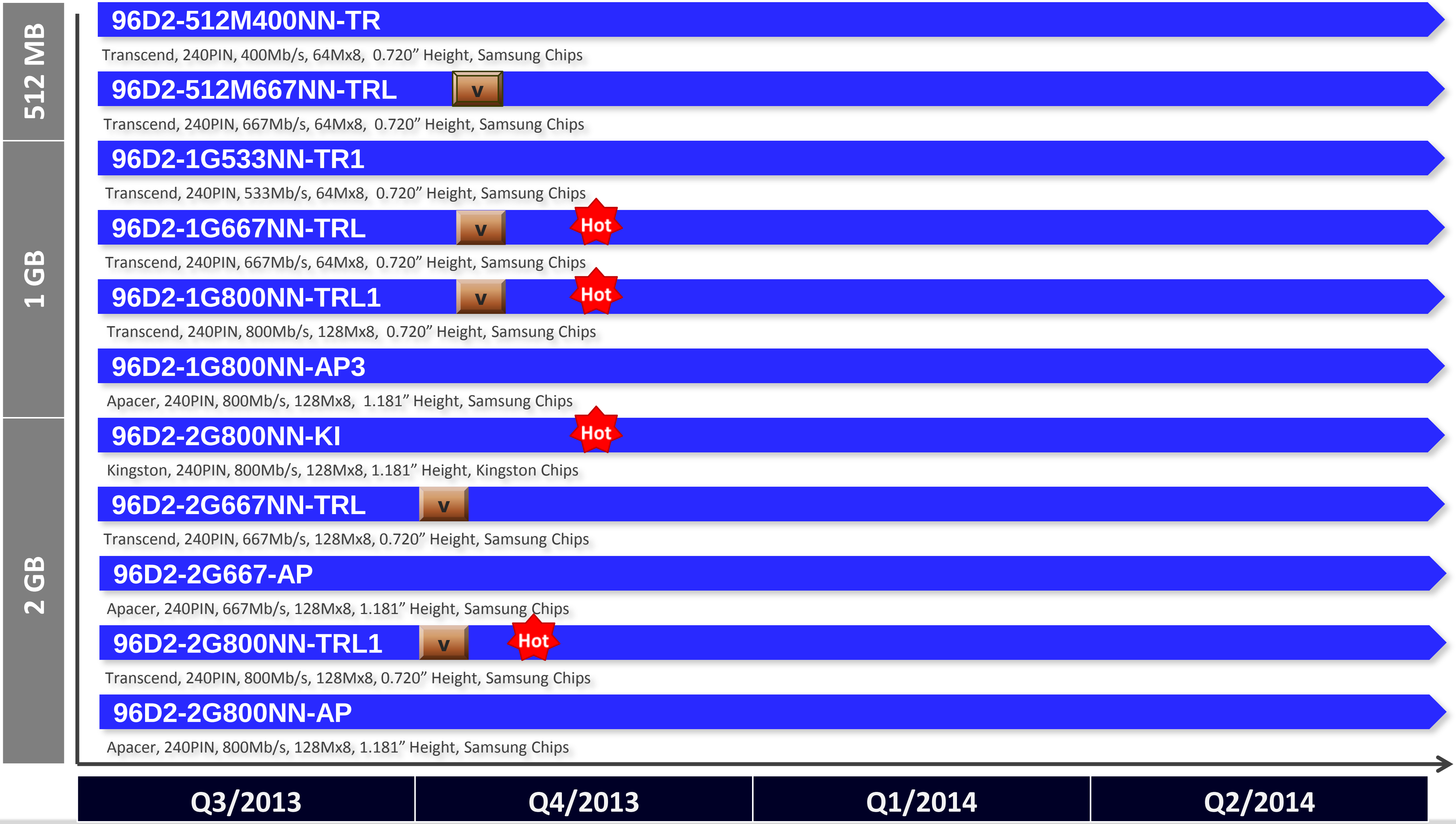
96SD-1G400NN-TR
Transcend, 200PIN, 400Mb/s, 64Mx8, 1.250” Height, Samsung Chips

96SD-1G400NN-AP1
Apacer, 200PIN, 400Mb/s, 64Mx8, 1.250” Height, Samsung Chips

Q3/2013 Q4/2013 Q1/2014 Q2/2014

DDR2 DIMM

▬	Available
▬	Phasing-out
▬	Planning
E	ECC
R	Registered
F	Fully Buffered
N	New
L	Low-Profile
V	Very Low-Profile
W	Wide Temperature



512 MB

96D2-512M400NN-TR
Transcend, 240PIN, 400Mb/s, 64Mx8, 0.720” Height, Samsung Chips

96D2-512M667NN-TRL V
Transcend, 240PIN, 667Mb/s, 64Mx8, 0.720” Height, Samsung Chips

1 GB

96D2-1G533NN-TR1
Transcend, 240PIN, 533Mb/s, 64Mx8, 0.720” Height, Samsung Chips

96D2-1G667NN-TRL V Hot
Transcend, 240PIN, 667Mb/s, 64Mx8, 0.720” Height, Samsung Chips

96D2-1G800NN-TRL1 V Hot
Transcend, 240PIN, 800Mb/s, 128Mx8, 0.720” Height, Samsung Chips

96D2-1G800NN-AP3
Apacer, 240PIN, 800Mb/s, 128Mx8, 1.181” Height, Samsung Chips

2 GB

96D2-2G800NN-KI Hot
Kingston, 240PIN, 800Mb/s, 128Mx8, 1.181” Height, Kingston Chips

96D2-2G667NN-TRL V
Transcend, 240PIN, 667Mb/s, 128Mx8, 0.720” Height, Samsung Chips

96D2-2G667-AP
Apacer, 240PIN, 667Mb/s, 128Mx8, 1.181” Height, Samsung Chips

96D2-2G800NN-TRL1 V Hot
Transcend, 240PIN, 800Mb/s, 128Mx8, 0.720” Height, Samsung Chips

96D2-2G800NN-AP
Apacer, 240PIN, 800Mb/s, 128Mx8, 1.181” Height, Samsung Chips

Q3/2013	Q4/2013	Q1/2014	Q2/2014

DDR2 DIMM Advance Feature

🟦 Available ▨ Phasing-out ▭ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature

ECC

1 GB

96D2-1G533E-TR E

Transcend, 240PIN, 533Mb/s, 64Mx8, 1.181” Height, Samsung Chips

2 GB

96D2-2G800E-AP1 E

Apacer, 240PIN, 800Mb/s, 128Mx8, 1.181” Height, Samsung Chips

96D2-2G800E-TR1 E

Transcend, 240PIN, 800Mb/s, 128Mx8, 1.181” Height, Samsung Chips

ECC and Registered

1 GB

96D2-1G400ER-TR E R

Transcend, 240PIN, 400Mb/s, 64Mx8, 1.181” Height, Samsung Chips

2 GB

96D2-2G667ER-TR E R

Transcend, 240PIN, 667Mb/s, 128Mx8, 1.181” Height, Samsung Chips

4 GB

96D2-4G667ER-TR1 E R

Transcend, 240PIN, 667Mb/s, 256Mx4, 1.181” Height, Samsung Chips

Q3/2013 Q4/2013 Q1/2014 Q2/2014

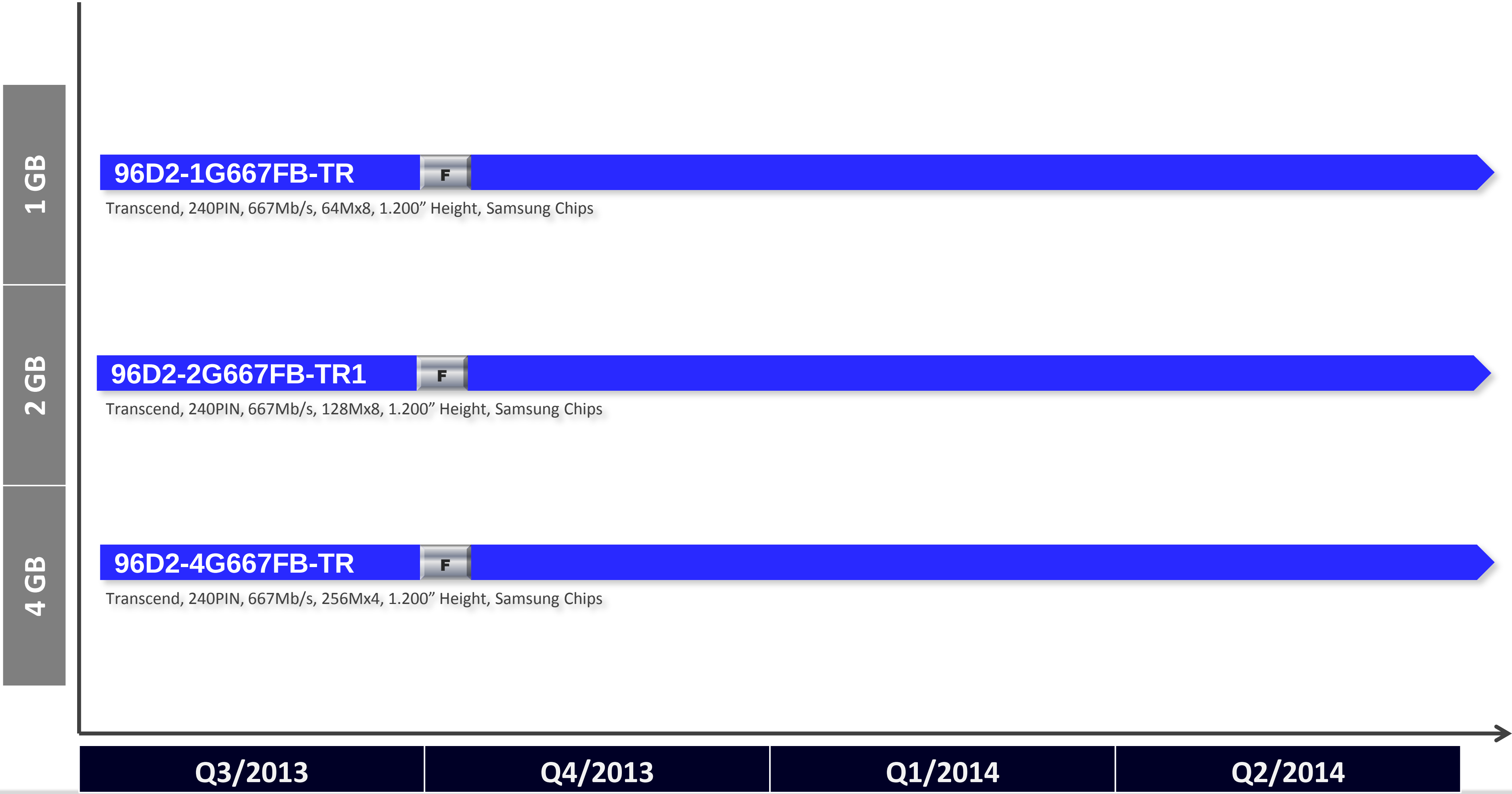
🟦 Available ▨ Phasing-out ▭ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature

DDR2 DIMM Advance Feature

Fully Buffered



96D2-1G667FB-TR

Transcend, 240PIN, 667Mb/s, 64Mx8, 1.200” Height, Samsung Chips

96D2-2G667FB-TR1

Transcend, 240PIN, 667Mb/s, 128Mx8, 1.200” Height, Samsung Chips

96D2-4G667FB-TR

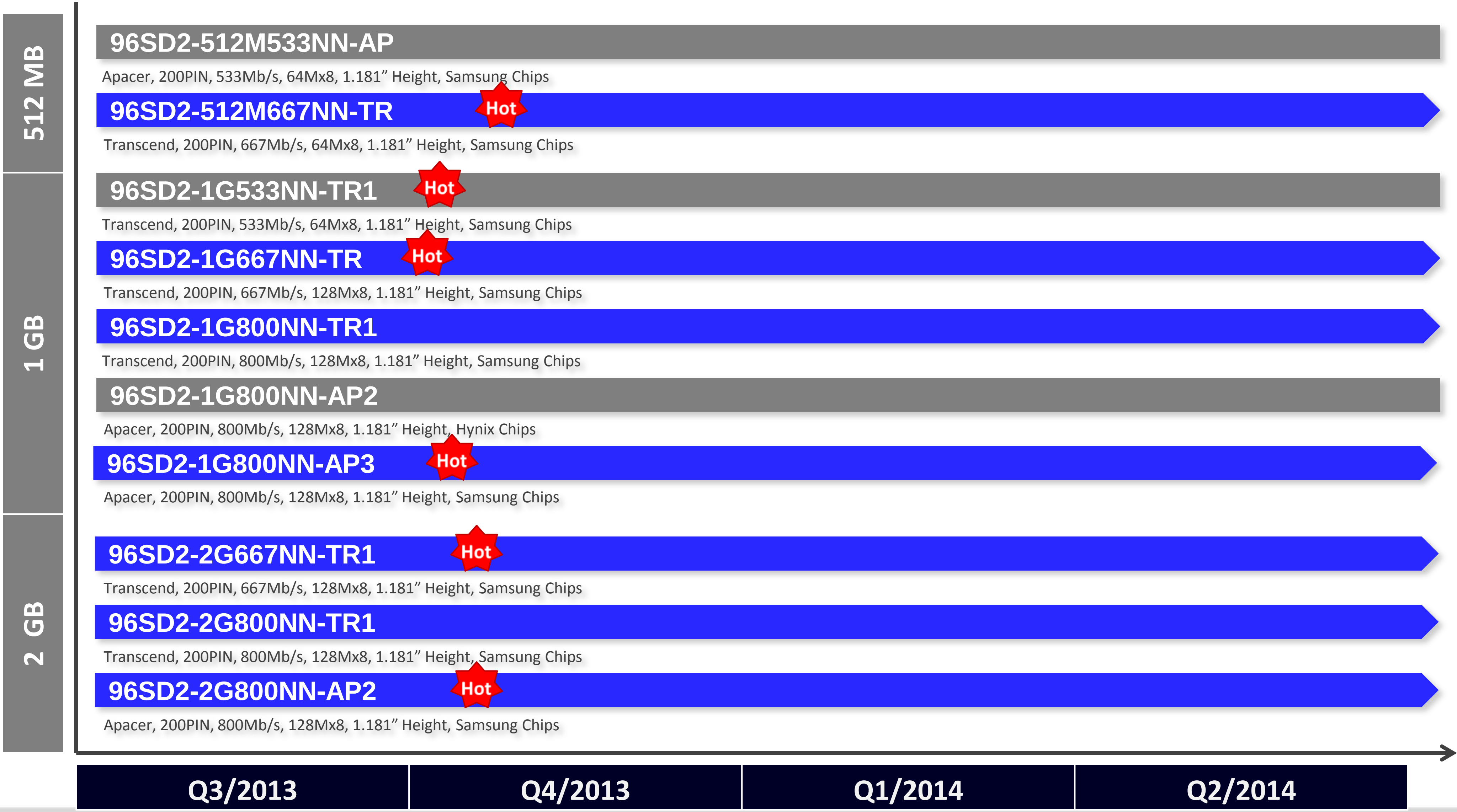
Transcend, 240PIN, 667Mb/s, 256Mx4, 1.200” Height, Samsung Chips

DDR2 SO-DIMM

🟦 Available ▨ Phasing-out ☐ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature



512 MB

96SD2-512M533NN-AP
Apacer, 200PIN, 533Mb/s, 64Mx8, 1.181” Height, Samsung Chips

96SD2-512M667NN-TR Hot
Transcend, 200PIN, 667Mb/s, 64Mx8, 1.181” Height, Samsung Chips

1 GB

96SD2-1G533NN-TR1 Hot
Transcend, 200PIN, 533Mb/s, 64Mx8, 1.181” Height, Samsung Chips

96SD2-1G667NN-TR Hot
Transcend, 200PIN, 667Mb/s, 128Mx8, 1.181” Height, Samsung Chips

96SD2-1G800NN-TR1
Transcend, 200PIN, 800Mb/s, 128Mx8, 1.181” Height, Samsung Chips

96SD2-1G800NN-AP2
Apacer, 200PIN, 800Mb/s, 128Mx8, 1.181” Height, Hynix Chips

96SD2-1G800NN-AP3 Hot
Apacer, 200PIN, 800Mb/s, 128Mx8, 1.181” Height, Samsung Chips

2 GB

96SD2-2G667NN-TR1 Hot
Transcend, 200PIN, 667Mb/s, 128Mx8, 1.181” Height, Samsung Chips

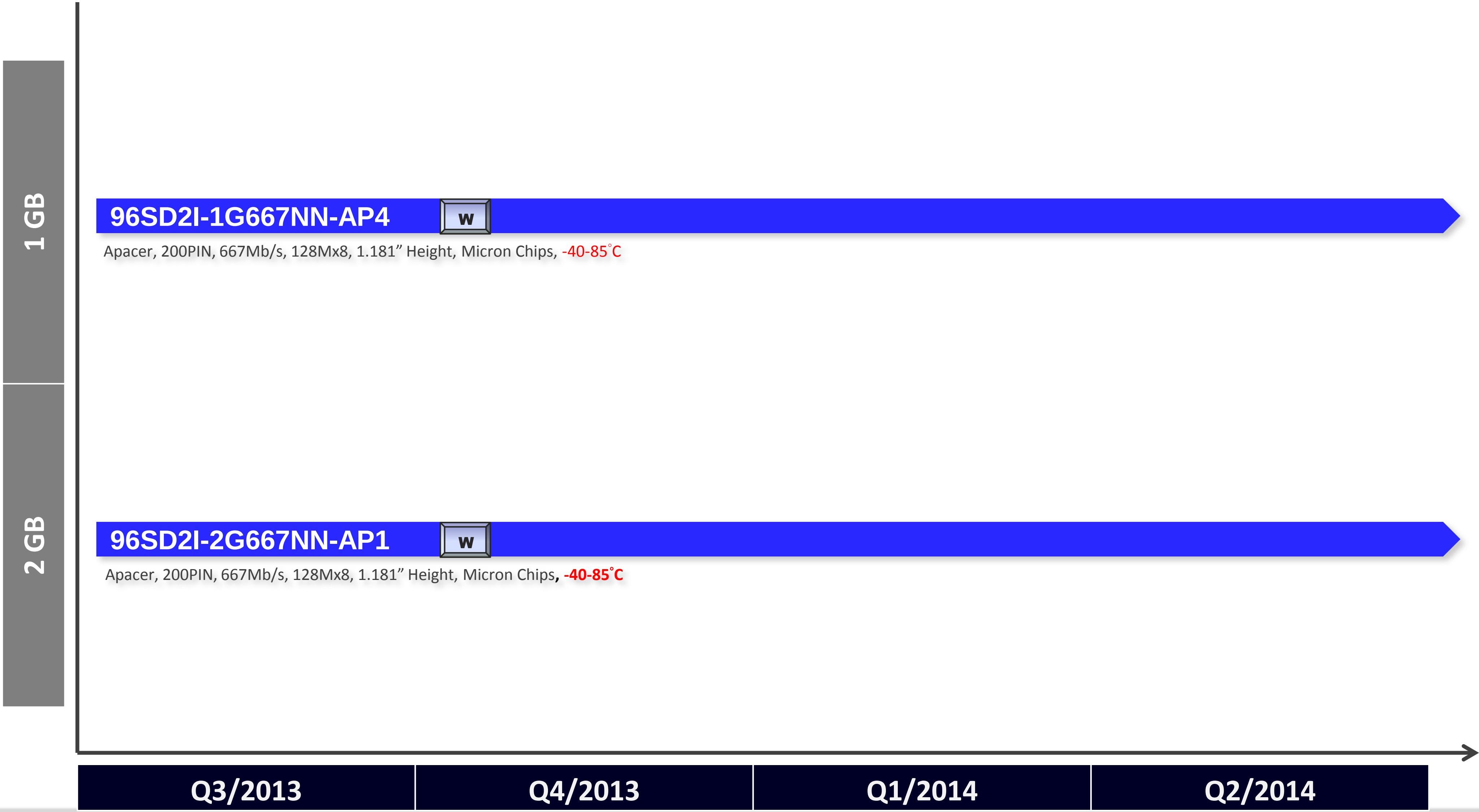
96SD2-2G800NN-TR1
Transcend, 200PIN, 800Mb/s, 128Mx8, 1.181” Height, Samsung Chips

96SD2-2G800NN-AP2 Hot
Apacer, 200PIN, 800Mb/s, 128Mx8, 1.181” Height, Samsung Chips

DDR2 SO-DIMM Wide Temp.

Available Phasing-out Planning

E ECC
R Registered
F Fully Buffered
N New
L Low-Profile
V Very Low-Profile
W Wide Temperature



96SD2I-1G667NN-AP4

Apacer, 200PIN, 667Mb/s, 128Mx8, 1.181” Height, Micron Chips, -40-85˚C

96SD2I-2G667NN-AP1

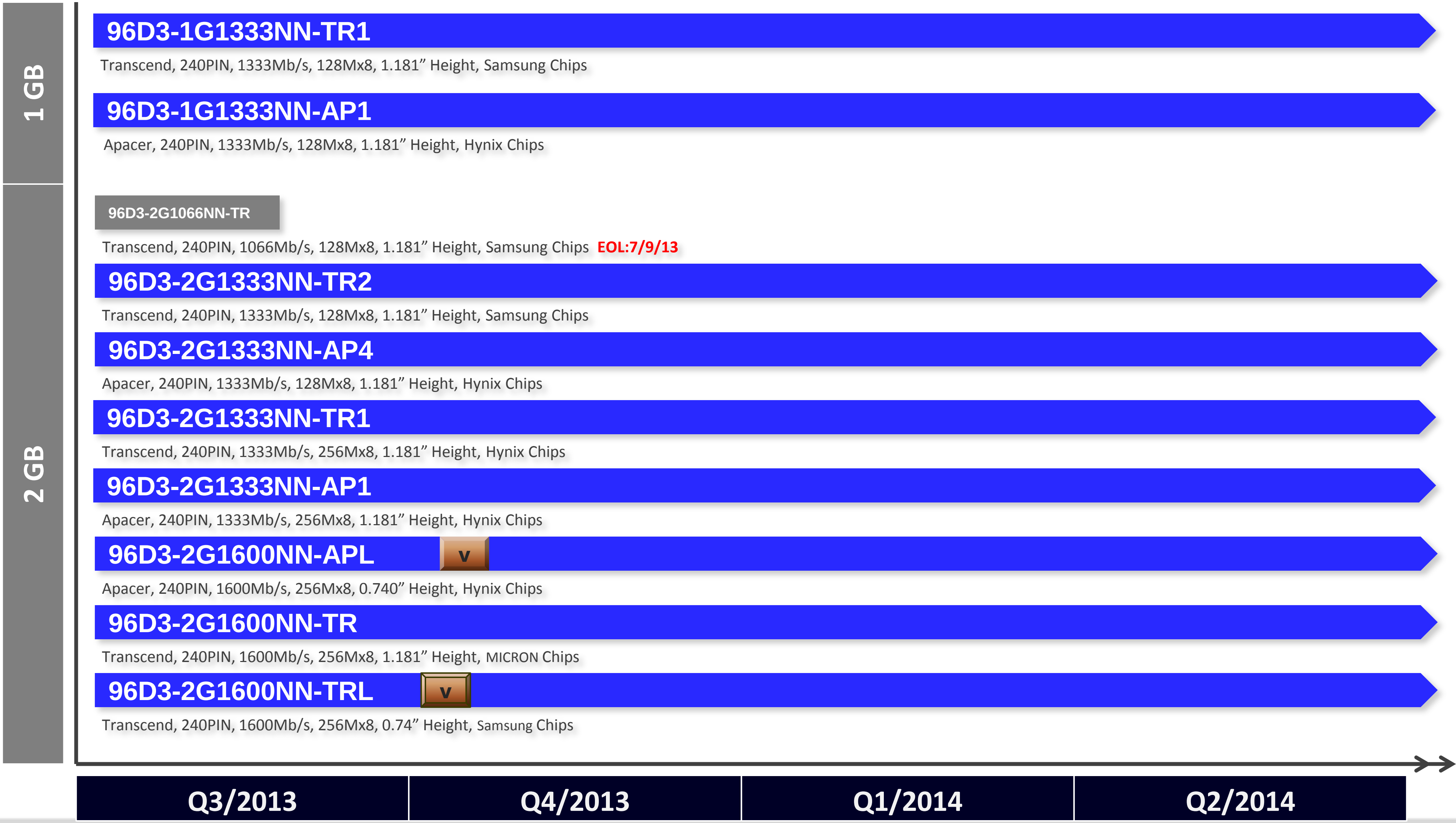
Apacer, 200PIN, 667Mb/s, 128Mx8, 1.181” Height, Micron Chips, **-40-85˚C**

🟦 Available ▨ Phasing-out ▭ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature

DDR3 DIMM



1 GB

96D3-1G1333NN-TR1

Transcend, 240PIN, 1333Mb/s, 128Mx8, 1.181" Height, Samsung Chips

96D3-1G1333NN-AP1

Apacer, 240PIN, 1333Mb/s, 128Mx8, 1.181" Height, Hynix Chips

2 GB

96D3-2G1066NN-TR

Transcend, 240PIN, 1066Mb/s, 128Mx8, 1.181" Height, Samsung Chips **EOL:7/9/13**

96D3-2G1333NN-TR2

Transcend, 240PIN, 1333Mb/s, 128Mx8, 1.181" Height, Samsung Chips

96D3-2G1333NN-AP4

Apacer, 240PIN, 1333Mb/s, 128Mx8, 1.181" Height, Hynix Chips

96D3-2G1333NN-TR1

Transcend, 240PIN, 1333Mb/s, 256Mx8, 1.181" Height, Hynix Chips

96D3-2G1333NN-AP1

Apacer, 240PIN, 1333Mb/s, 256Mx8, 1.181" Height, Hynix Chips

96D3-2G1600NN-APL V

Apacer, 240PIN, 1600Mb/s, 256Mx8, 0.740" Height, Hynix Chips

96D3-2G1600NN-TR

Transcend, 240PIN, 1600Mb/s, 256Mx8, 1.181" Height, MICRON Chips

96D3-2G1600NN-TRL V

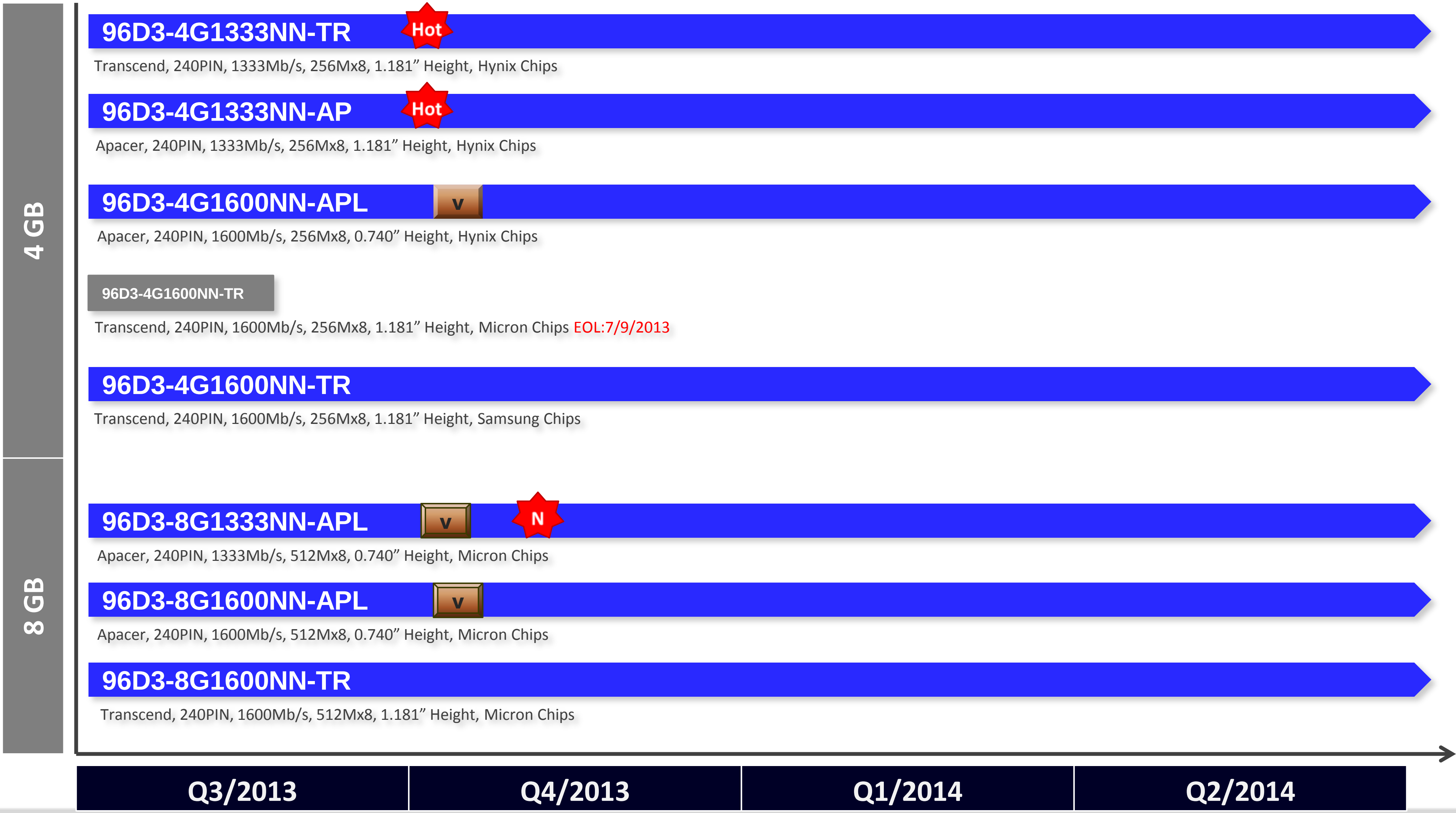
Transcend, 240PIN, 1600Mb/s, 256Mx8, 0.74" Height, Samsung Chips

DDR3 DIMM

🟦 Available ▨ Phasing-out 🟦 Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature



96D3-4G1333NN-TR Hot

Transcend, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96D3-4G1333NN-AP Hot

Apacer, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96D3-4G1600NN-APL V

Apacer, 240PIN, 1600Mb/s, 256Mx8, 0.740” Height, Hynix Chips

96D3-4G1600NN-TR

Transcend, 240PIN, 1600Mb/s, 256Mx8, 1.181” Height, Micron Chips EOL:7/9/2013

96D3-4G1600NN-TR

Transcend, 240PIN, 1600Mb/s, 256Mx8, 1.181” Height, Samsung Chips

96D3-8G1333NN-APL V N

Apacer, 240PIN, 1333Mb/s, 512Mx8, 0.740” Height, Micron Chips

96D3-8G1600NN-APL V

Apacer, 240PIN, 1600Mb/s, 512Mx8, 0.740” Height, Micron Chips

96D3-8G1600NN-TR

Transcend, 240PIN, 1600Mb/s, 512Mx8, 1.181” Height, Micron Chips

Q3/2013	Q4/2013	Q1/2014	Q2/2014

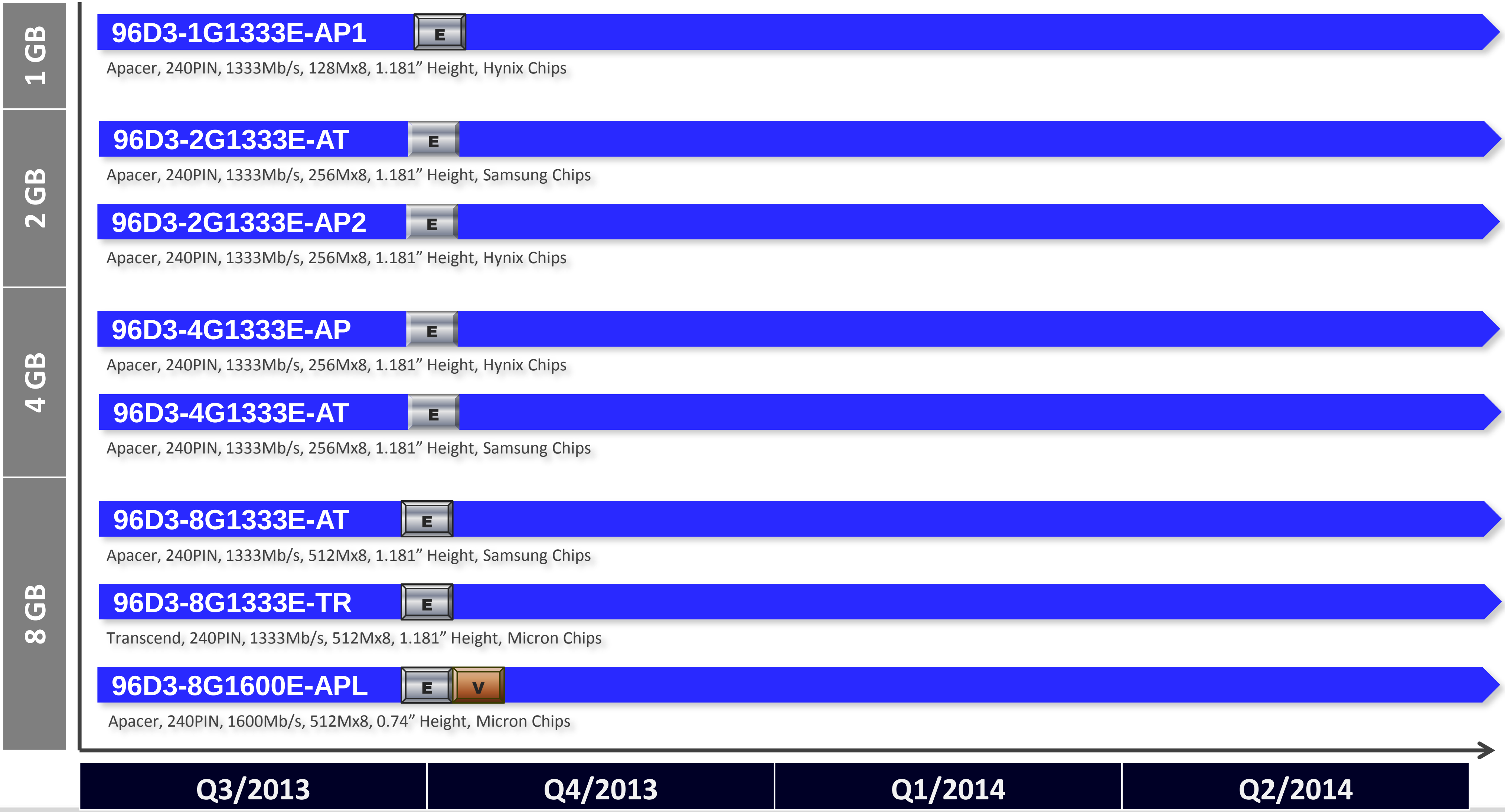
DDR3 DIMM Advance Feature

🟦 Available ▨ Phasing-out ▭ Planning

E ECC **R** Registered **F** Fully Buffered **N** New

L Low-Profile **V** Very Low-Profile **W** Wide Temperature

ECC



1 GB

96D3-1G1333E-AP1 E

Apacer, 240PIN, 1333Mb/s, 128Mx8, 1.181” Height, Hynix Chips

2 GB

96D3-2G1333E-AT E

Apacer, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Samsung Chips

96D3-2G1333E-AP2 E

Apacer, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

4 GB

96D3-4G1333E-AP E

Apacer, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96D3-4G1333E-AT E

Apacer, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Samsung Chips

8 GB

96D3-8G1333E-AT E

Apacer, 240PIN, 1333Mb/s, 512Mx8, 1.181” Height, Samsung Chips

96D3-8G1333E-TR E

Transcend, 240PIN, 1333Mb/s, 512Mx8, 1.181” Height, Micron Chips

96D3-8G1600E-APL E V

Apacer, 240PIN, 1600Mb/s, 512Mx8, 0.74” Height, Micron Chips

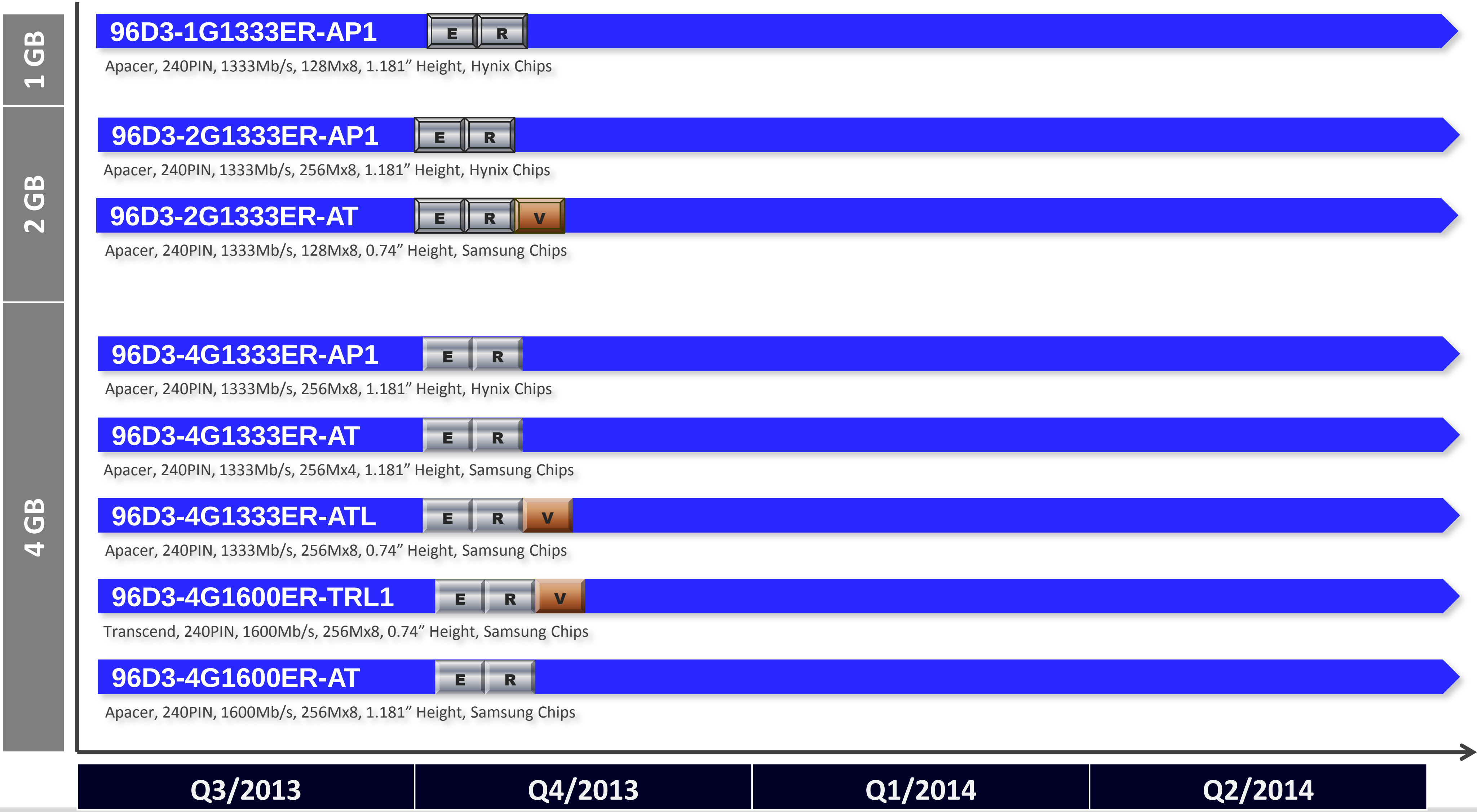
DDR3 DIMM Advance Feature

ECC and Registered

🟦 Available ⬜ Phasing-out 🟦 Planning

E ECC **R** Registered **F** Fully Buffered **N** New

L Low-Profile **V** Very Low-Profile **W** Wide Temperature



96D3-1G1333ER-AP1 E R

Apacer, 240PIN, 1333Mb/s, 128Mx8, 1.181” Height, Hynix Chips

96D3-2G1333ER-AP1 E R

Apacer, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96D3-2G1333ER-AT E R V

Apacer, 240PIN, 1333Mb/s, 128Mx8, 0.74” Height, Samsung Chips

96D3-4G1333ER-AP1 E R

Apacer, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96D3-4G1333ER-AT E R

Apacer, 240PIN, 1333Mb/s, 256Mx4, 1.181” Height, Samsung Chips

96D3-4G1333ER-ATL E R V

Apacer, 240PIN, 1333Mb/s, 256Mx8, 0.74” Height, Samsung Chips

96D3-4G1600ER-TRL1 E R V

Transcend, 240PIN, 1600Mb/s, 256Mx8, 0.74” Height, Samsung Chips

96D3-4G1600ER-AT E R

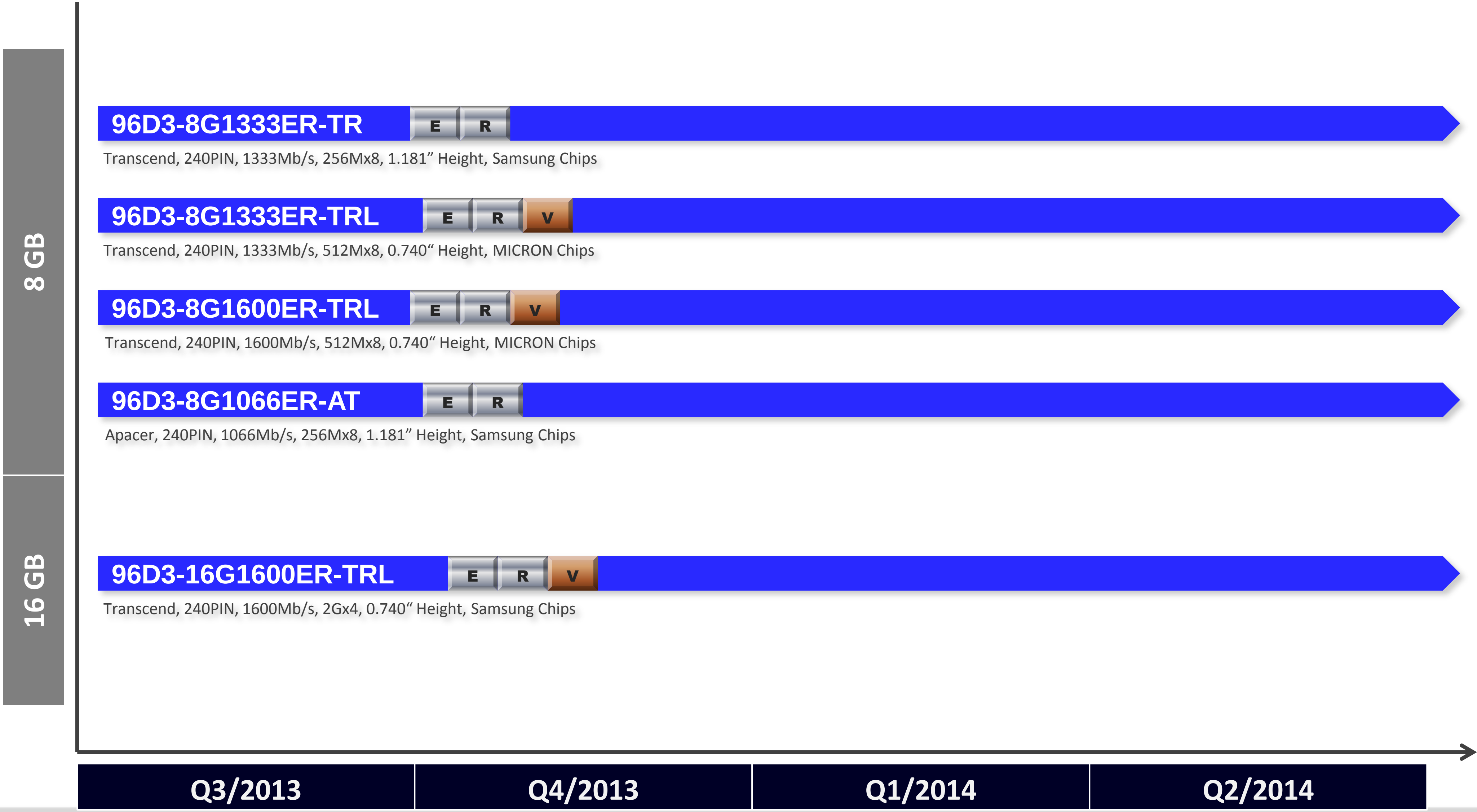
Apacer, 240PIN, 1600Mb/s, 256Mx8, 1.181” Height, Samsung Chips

DDR3 DIMM Advance Feature

ECC and Registered

▬ Available ▬ Phasing-out ▬ Planning

E ECC
R Registered
F Fully Buffered
N New
L Low-Profile
V Very Low-Profile
W Wide Temperature



Transcend, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Samsung Chips

Transcend, 240PIN, 1333Mb/s, 512Mx8, 0.740“ Height, MICRON Chips

Transcend, 240PIN, 1600Mb/s, 512Mx8, 0.740“ Height, MICRON Chips

Apacer, 240PIN, 1066Mb/s, 256Mx8, 1.181” Height, Samsung Chips

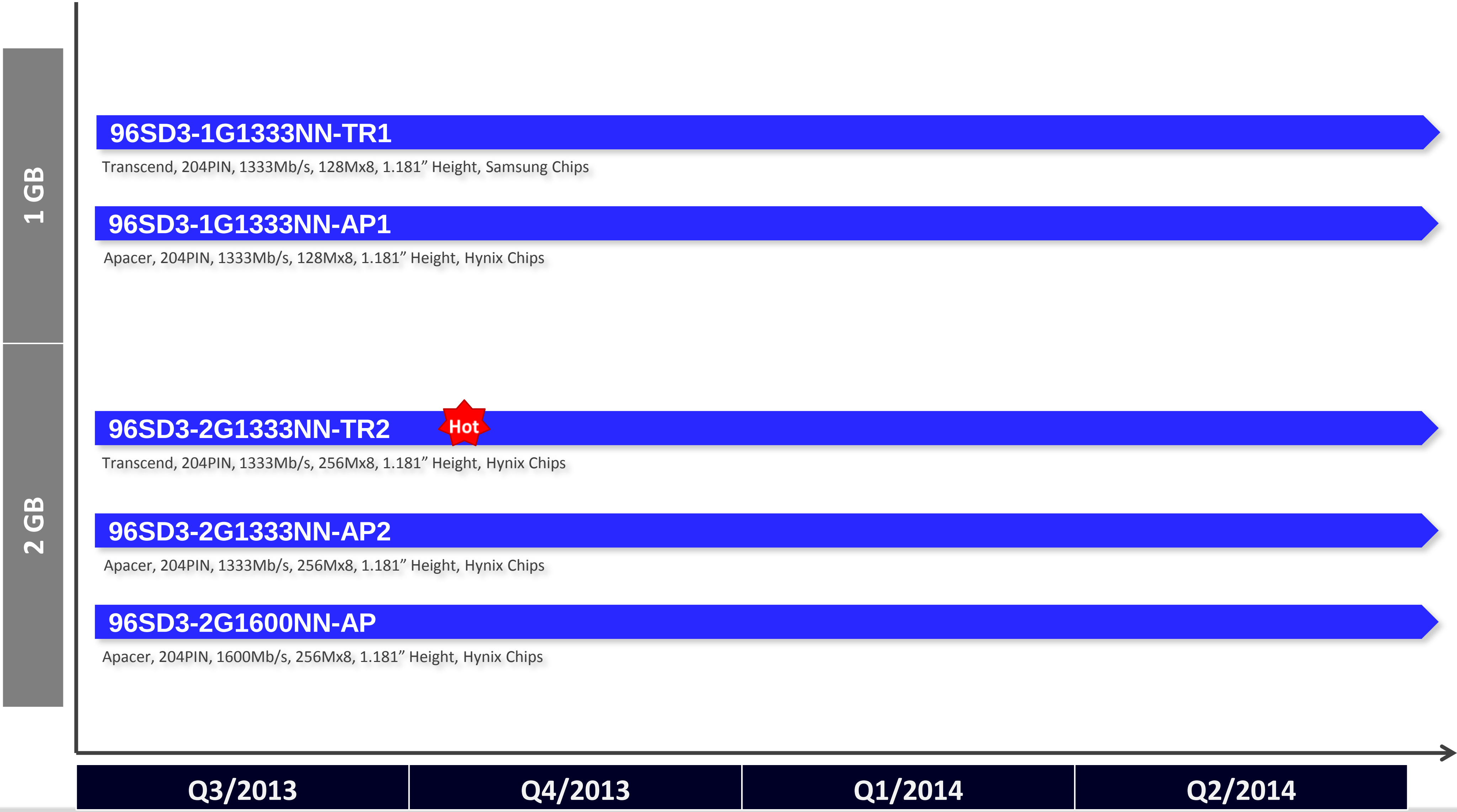
Transcend, 240PIN, 1600Mb/s, 2Gx4, 0.740“ Height, Samsung Chips

DDR3 SO-DIMM

🟦 Available ▨ Phasing-out 🟦 Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature



1 GB

96SD3-1G1333NN-TR1

Transcend, 204PIN, 1333Mb/s, 128Mx8, 1.181” Height, Samsung Chips

96SD3-1G1333NN-AP1

Apacer, 204PIN, 1333Mb/s, 128Mx8, 1.181” Height, Hynix Chips

2 GB

96SD3-2G1333NN-TR2 Hot

Transcend, 204PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96SD3-2G1333NN-AP2

Apacer, 204PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96SD3-2G1600NN-AP

Apacer, 204PIN, 1600Mb/s, 256Mx8, 1.181” Height, Hynix Chips

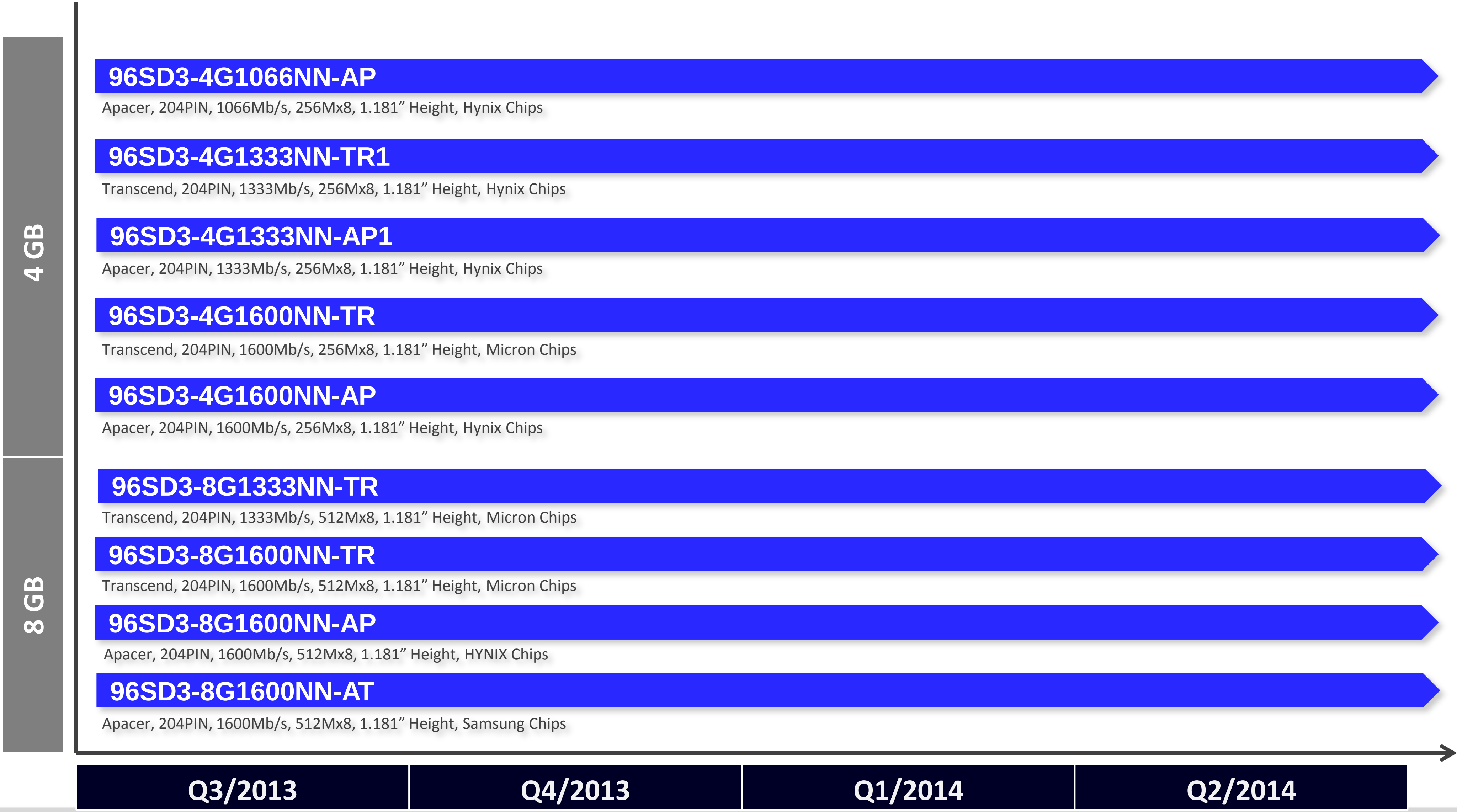
Q3/2013	Q4/2013	Q1/2014	Q2/2014

DDR3 SO-DIMM

🟦 Available ▨ Phasing-out 🟦 Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature



4 GB

96SD3-4G1066NN-AP

Apacer, 204PIN, 1066Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96SD3-4G1333NN-TR1

Transcend, 204PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96SD3-4G1333NN-AP1

Apacer, 204PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96SD3-4G1600NN-TR

Transcend, 204PIN, 1600Mb/s, 256Mx8, 1.181” Height, Micron Chips

96SD3-4G1600NN-AP

Apacer, 204PIN, 1600Mb/s, 256Mx8, 1.181” Height, Hynix Chips

8 GB

96SD3-8G1333NN-TR

Transcend, 204PIN, 1333Mb/s, 512Mx8, 1.181” Height, Micron Chips

96SD3-8G1600NN-TR

Transcend, 204PIN, 1600Mb/s, 512Mx8, 1.181” Height, Micron Chips

96SD3-8G1600NN-AP

Apacer, 204PIN, 1600Mb/s, 512Mx8, 1.181” Height, HYNIX Chips

96SD3-8G1600NN-AT

Apacer, 204PIN, 1600Mb/s, 512Mx8, 1.181” Height, Samsung Chips

Q3/2013	Q4/2013	Q1/2014	Q2/2014

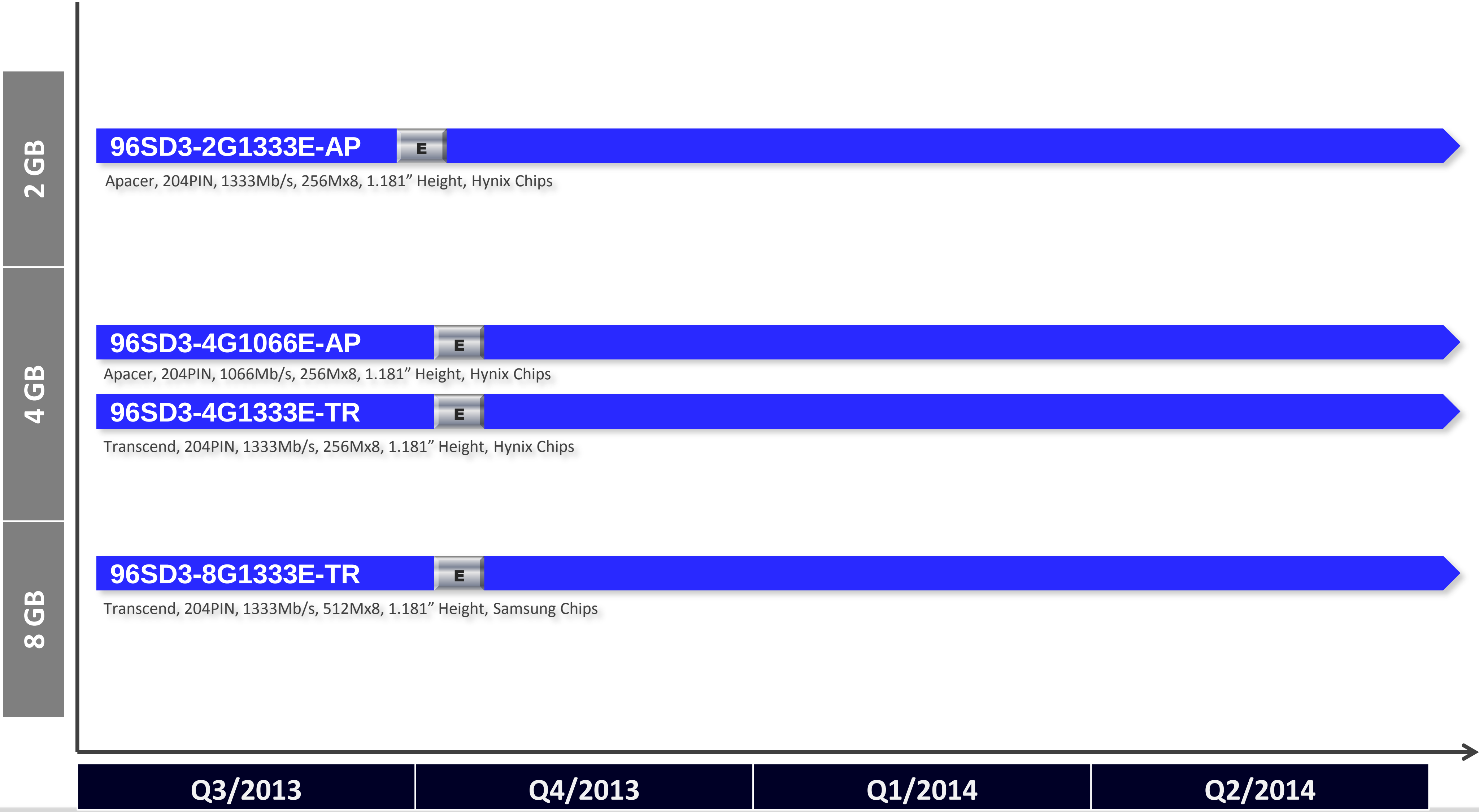
DDR3 SO-DIMM

Advance Feature - ECC

🟦 Available ▨ Phasing-out 🟦 Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature



96SD3-2G1333E-AP E

Apacer, 204PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96SD3-4G1066E-AP E

Apacer, 204PIN, 1066Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96SD3-4G1333E-TR E

Transcend, 204PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96SD3-8G1333E-TR E

Transcend, 204PIN, 1333Mb/s, 512Mx8, 1.181” Height, Samsung Chips

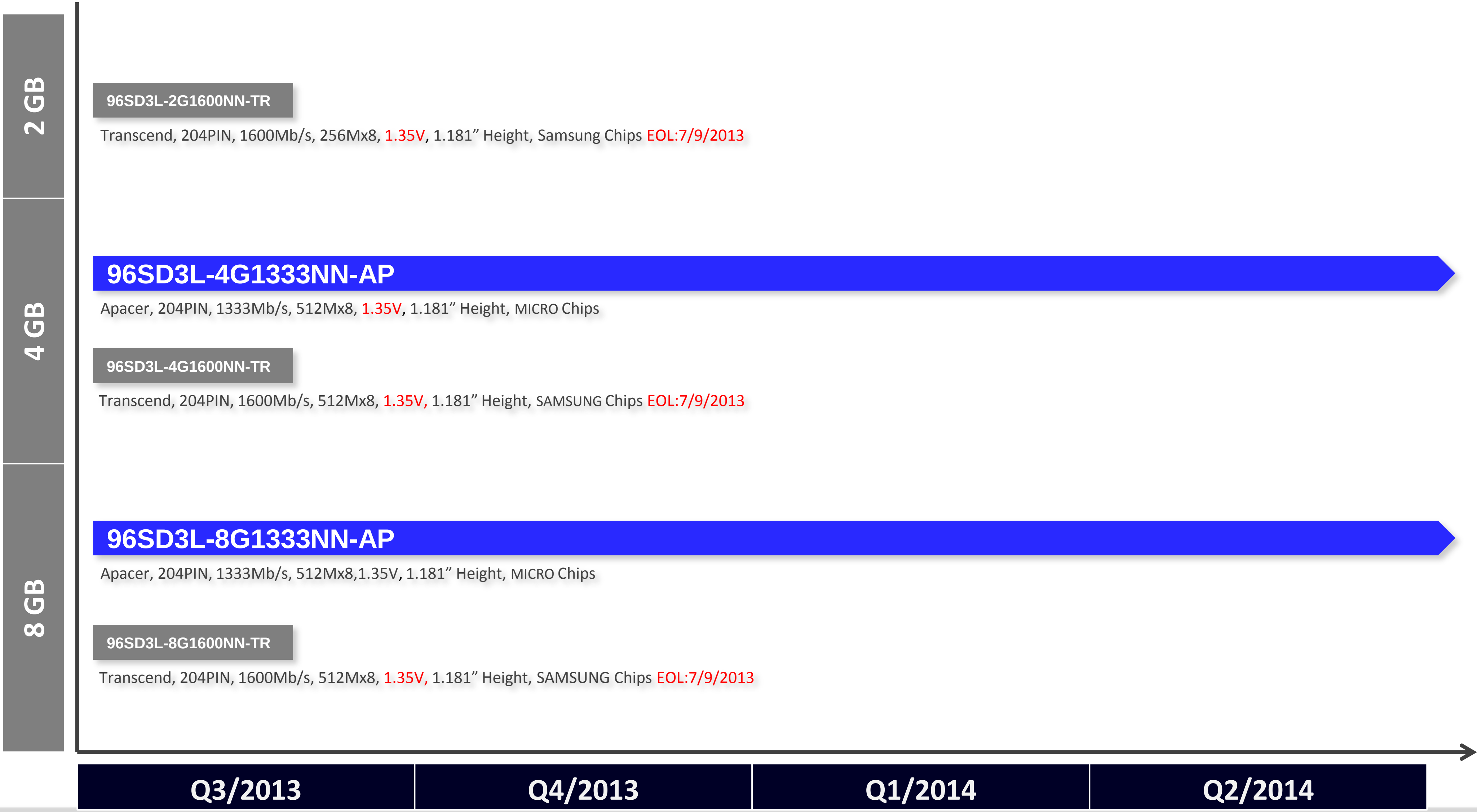
DDR3 SO-DIMM

Low Voltage.

🟦 Available ▨ Phasing-out ▭ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature



2 GB

96SD3L-2G1600NN-TR

Transcend, 204PIN, 1600Mb/s, 256Mx8, 1.35V, 1.181” Height, Samsung Chips EOL:7/9/2013

4 GB

96SD3L-4G1333NN-AP

Apacer, 204PIN, 1333Mb/s, 512Mx8, 1.35V, 1.181” Height, MICRO Chips

96SD3L-4G1600NN-TR

Transcend, 204PIN, 1600Mb/s, 512Mx8, 1.35V, 1.181” Height, SAMSUNG Chips EOL:7/9/2013

8 GB

96SD3L-8G1333NN-AP

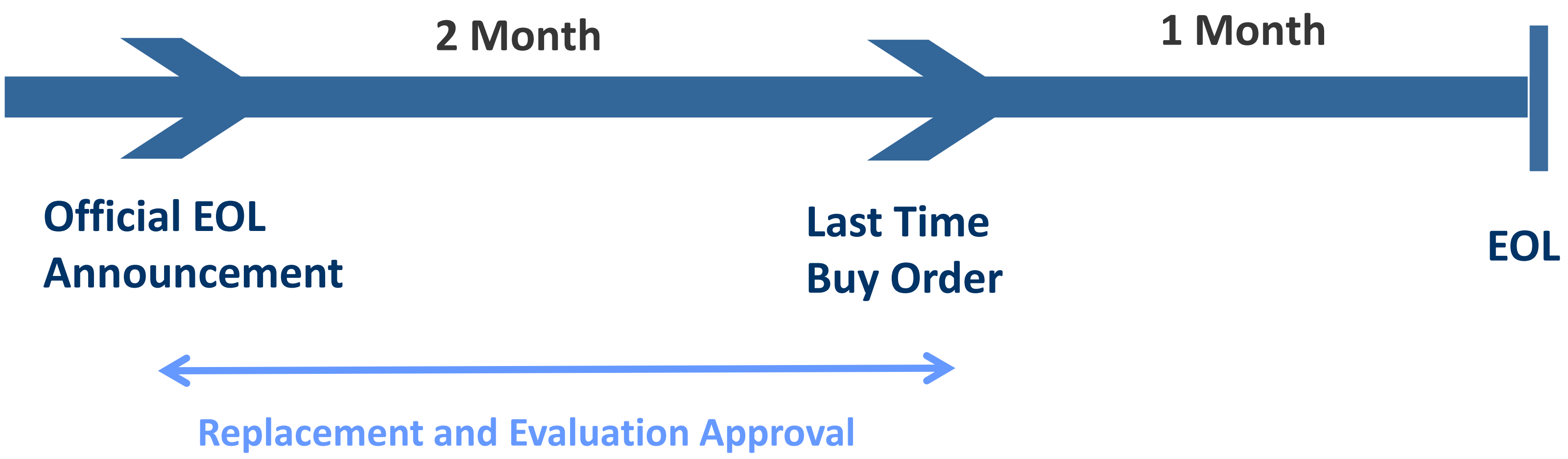
Apacer, 204PIN, 1333Mb/s, 512Mx8,1.35V, 1.181” Height, MICRO Chips

96SD3L-8G1600NN-TR

Transcend, 204PIN, 1600Mb/s, 512Mx8, 1.35V, 1.181” Height, SAMSUNG Chips EOL:7/9/2013

Memory EOL Procedure

- **For support and product management optimization, PAPS will follow the Memory phase-out procedure as below.**



2 Month

1 Month

Official EOL Announcement

Last Time Buy Order

EOL

Replacement and Evaluation Approval

Thank you

Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.

Как с нами связаться

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Электронная почта: org@eplast1.ru
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